



# High Voltage, Isolated IGBT Gate Driver with Fault Detection

## Data Sheet

## ADuM4137

### FEATURES

- 6 A peak drive output capability**
- Internal turn off NFET, on resistance:  $<0.95\ \Omega$**
- Internal turn on PFET, on resistance:  $<1.18\ \Omega$**
- Split emitter overcurrent detection**
- Miller clamp output with gate sense input**
- Isolated fault output**
- Isolated temperature sensor read back**
- Propagation delay**
  - Rising: 105 ns typical**
  - Falling: 107 ns typical**
- Minimum pulse width: 70 ns**
- Operating junction temperature range ( $-40^{\circ}\text{C}$  to  $+150^{\circ}\text{C}$ )**
- $V_{DD1}$  and  $V_{DD2}$  UVLO**
- ASC input**
- 8.3 mm creepage distance**
- Safety and regulatory approvals**
  - 5 kV rms for 1 minute per UL 1577**
  - CSA Component Acceptance Notice 5A**
  - DIN V VDE V 0884-10 (VDE V 0884-10):2006-12**
- $V_{IORM} = 849\ V_{PEAK}$  (reinforced/basic)**
- AEC-Q100 qualified for automotive applications**

### APPLICATIONS

- MOSFET/IGBT gate drivers**
- Photovoltaic (PV) inverters**
- Motor drives**
- Power supplies**

### GENERAL DESCRIPTION

The ADuM4137<sup>1</sup> is a single-channel gate driver specifically optimized for driving insulated gate bipolar transistors (IGBTs). Analog Devices, Inc., iCoupler® technology provides isolation between the input signal and the output gate drive.

The Analog Devices chip scale transformers also provide isolated communication of control information between the high voltage and low voltage domains of the chip. Information on the status of the chip can be read back from the dedicated fault outputs. The ADuM4137 provides isolated fault reporting for overcurrent events, remote temperature overheating events, undervoltage lockout (UVLO), and thermal shutdown (TSD).

Integrated onto the ADuM4137 is an overcurrent detection feature that protects the IGBT in case of overcurrent events. The split emitter overcurrent detection is coupled with a high speed, two-level turn off in case of faults.

The ADuM4137 provides a Miller clamp control signal for the external metal-oxide semiconductor field effect transistor (MOSFET) to provide robust IGBT turn off with a single rail supply when the gate voltage drops below 2.0 V (typical) and above GND<sub>2</sub>. Operation with unipolar secondary supplies is possible, with or without the Miller clamp operation.

A low gate voltage detection circuit can trigger a fault if the gate voltage does not go above the internal threshold ( $V_{VL}$ ) within the time allowed from turn on ( $t_{DVL}$ ). This circuit allows detection of IGBT device failures that exhibit gate shorts or other causes of weak drive.

The secondary falling UVLO is set to 11.24 V (typical) for common IGBT two-level plateau voltage levels.

The ADuM4137 provides for in field programming of temperature. Two temperature sensor pins allow isolated monitoring of system temperatures at the IGBTs, sensing diode gains and offsets by means of a serial port interface (SPI) bus on the primary side of the device. Values are stored on an EEPROM located on the secondary side. Additionally, programming is available for specific voltage offsets, temperature sensing reporting frequencies, and important delays.

The ASC pin on the secondary side on the ADuM4137 allows the driver to be switched on from the secondary side if no faults are present.

<sup>1</sup> Protected by U.S. Patents 5,952,849; 6,873,065; and 7,075,329. Other patents pending.

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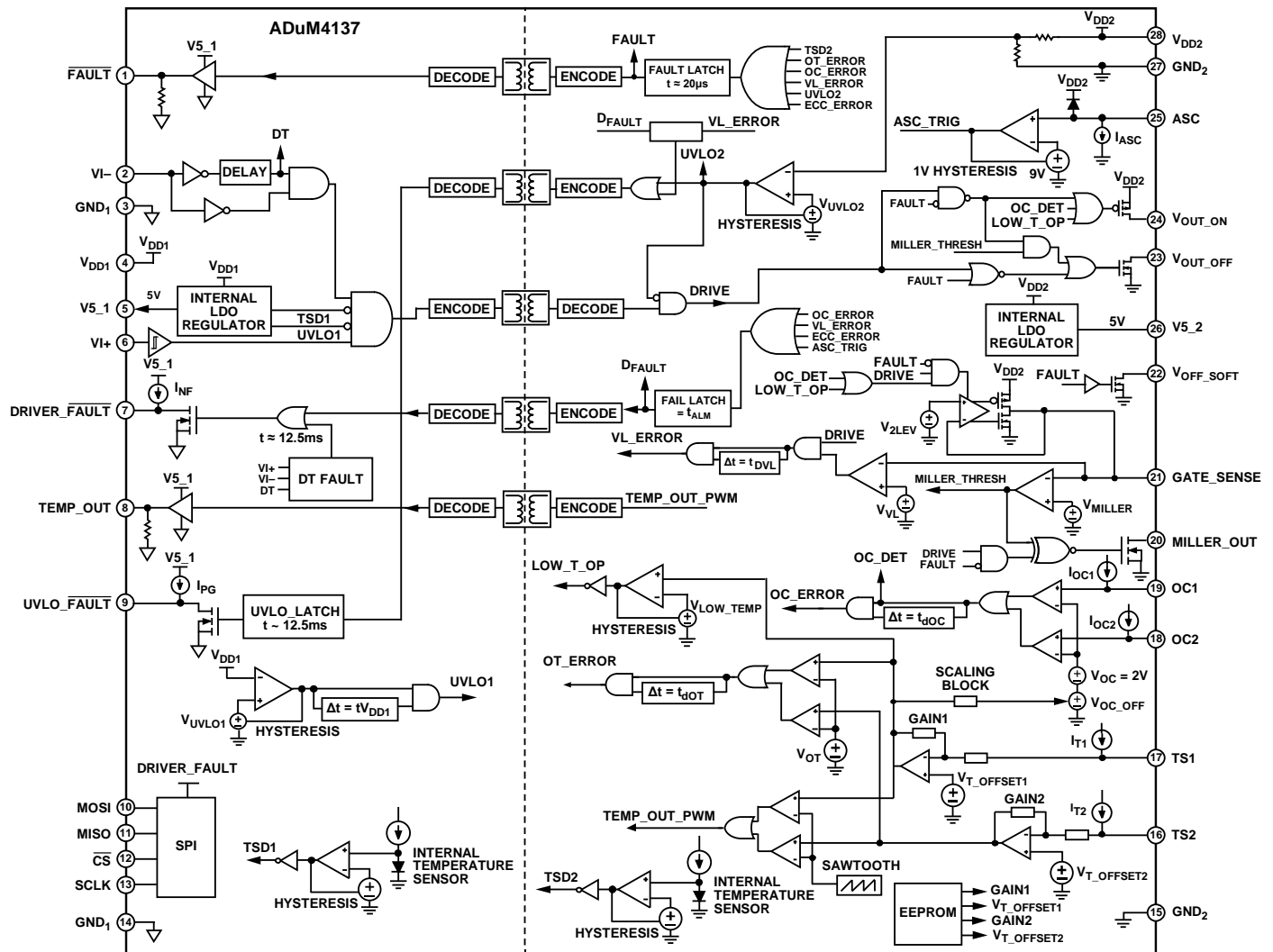
## REVISION HISTORY

### 8/2019—Rev. 0 to Rev. A

Change to Features Section .....	1
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### 2/2019—Revision 0: Initial Version

## FUNCTIONAL BLOCK DIAGRAM



## NOTES

1. VL\_ERROR IS THE VOLTAGE LOW ERROR INTERNAL CONNECTION.
2. TEMP\_OUT\_PWM IS THE TEMPERATURE SENSE INTERNAL CONNECTION.
3. OC\_ERROR IS THE OVERCURRENT ERROR INTERNAL CONNECTION.
4. OC\_DET IS THE OVERCURRENT DETECTION INTERNAL CONNECTION.
5. V<sub>VL</sub> IS THE GATE LOW VOLTAGE REFERENCE VOLTAGE.
6. ASC\_TRIG IS THE ASC SIGNAL INTERNAL CONNECTION.
7. MILLER\_THRESH IS THE MILLER CLAMP ACTIVATION INTERNAL CONNECTION.
8. OT\_ERROR IS THE OVERTEMPERATURE ERROR INTERNAL CONNECTION.
9. V<sub>T\_OFFSET1</sub> IS THE TEMPERATURE SENSE OFFSET VOLTAGE FOR THE TS1 PIN.
10. V<sub>T\_OFFSET2</sub> IS THE TEMPERATURE SENSE OFFSET VOLTAGE FOR TS2 PIN.
11. I<sub>T1</sub> IS THE INTERNAL CURRENT REFERENCE FOR TS1 PIN.
12. I<sub>T2</sub> IS THE INTERNAL CURRENT REFERENCE FOR TS2 PIN.
13. V<sub>OC\_OFF</sub> IS THE OVERCURRENT VOLTAGE OFFSET DUE TO TEMPERATURE RAMP.
14. V<sub>OC</sub> IS THE OVERCURRENT REFERENCE VOLTAGE.
15. I<sub>OC1</sub> IS THE OC1 INTERNAL PULL-UP CURRENT SOURCE.
16. I<sub>OC2</sub> IS THE OC2 INTERNAL PULL-UP CURRENT SOURCE.
17. V<sub>UVLO1</sub> IS THE VDD1 UVLO REFERENCE.
18. V<sub>UVLO2</sub> IS THE VDD2 UVLO REFERENCE.
19. V<sub>LOW\_TEMP</sub> IS THE LOW TEMPERATURE OPERATION REFERENCE.
20. V<sub>2LEV</sub> IS THE TARGET VOLTAGE REFERENCE FOR TWO LEVEL OPERATION.
21. LOW\_T\_OP IS THE LOW TEMPERATURE OPERATION TRIGGER.
22. DT IS THE DEADTIME INTERNAL CONNECTION.
23. D\_FAULT IS THE DRIVE FAULT INTERNAL CONNECTION.
24. UVLO\_LATCH IS THE UNDERVOLTAGE LOCKOUT LATCH TIMER.
25. GAIN1 IS THE REMOTE TEMPERATURE SENSE USER TRIMMABLE GAIN FOR TS1.
26. GAIN2 IS THE REMOTE TEMPERATURE SENSE USER TRIMMABLE GAIN FOR TS2.
27. TSD1 IS THE PRIMARY SIDE THERMAL SHUTDOWN COMMAND.
28. TSD2 IS THE SECONDARY SIDE THERMAL SHUTDOWN COMMAND.
29. V<sub>MILLER</sub> IS THE MILLER CLAMP REFERENCE VOLTAGE.
30. I<sub>INF</sub> IS THE DRIVER\_FAULT INTERNAL PULL-UP CURRENT SOURCE.
31. I<sub>PG</sub> IS THE UVLO\_FAULT INTERNAL PULL-UP CURRENT SOURCE.
32. I<sub>OT</sub> IS THE TEMPERATURE SENSE OVERTEMPERATURE REFERENCE.
33. I<sub>ASC</sub> IS THE ASC PIN INTERNAL PULL-UP CURRENT SOURCE.
34. ECC\_ERROR IS THE ERROR CORRECTING CODE INTERNAL CONNECTION.
35. t<sub>ALM</sub> IS THE FAULT LATCH HOLD TIME.
36. UVLO1 IS THE PRIMARY SIDE UVLO INTERNAL CONNECTION.
37. UVLO2 IS THE SECONDARY SIDE UVLO INTERNAL CONNECTION.

Figure 1.

17/037-001

## SPECIFICATIONS

### ELECTRICAL CHARACTERISTICS

Low-side voltages referenced to GND<sub>I</sub>, high-side voltages referenced to GND<sub>2</sub>, V<sub>DD1</sub> = 12 V, V<sub>DD2</sub> = 15 V, T<sub>J</sub> = -40°C to +150°C, unless otherwise noted. All minimum and maximum specifications apply over the entire recommended operating temperature range, unless otherwise noted. All typical specifications are at T<sub>J</sub> = 25°C, V<sub>DD1</sub> = 12 V, and V<sub>DD2</sub> = 15 V, unless otherwise noted.

Table 1.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
DC SPECIFICATIONS						
High-Side Power Supply						
Input Voltage, Secondary Side	V <sub>DD2</sub>	12		25	V	
V <sub>DD2</sub> Input Current, Quiescent	I <sub>DD2 (Q)</sub>	9.8	11.5	16.0	mA	TS1 = TS2 = open, VI+ = 0 V, VI− = 5 V, V <sub>DD2</sub> = 25 V
		12.8	15.2	20.0	mA	TS1 = TS2 = 2 V, VI+ = 5 V, VI− = 0 V, V <sub>DD2</sub> = 25 V
V5_2 Regulated Output Voltage	V <sub>V5_2</sub>	4.9	5.0	5.1	V	Unloaded
Logic Supply						
Input Voltage, Primary Side	V <sub>DD1</sub>	4.5		25	V	
V <sub>DD1</sub> Input Current	I <sub>DD1</sub>	2.8	3.8	4.7	mA	TS1 = TS2 = open, VI+ = 0 V, VI− = 5 V, TEMP_OUT floating, V <sub>DD1</sub> = 4.5 V, V <sub>DD2</sub> = 15 V
		3.3	6.3	8.5	mA	TS1 = TS2 = 2 V, VI+ = 5 V, VI− = 0 V, TEMP_OUT floating, V <sub>DD1</sub> = 25 V, V <sub>DD2</sub> = 15 V
V5_1 Regulated Output Voltage	V <sub>V5_1</sub>	4.9	5.0	5.1	V	Unloaded
Logic Inputs, VI+, VI−, $\overline{\text{CS}}$ , MOSI, SCLK						
Input Current (VI+, VI−, $\overline{\text{CS}}$ , MOSI, SCLK Only)	I <sub>I</sub>	−0.1	+0.01	+0.1	μA	
Input Voltage						
Logic High	V <sub>IH</sub>	2.5			V	V <sub>DD1</sub> ≥ 6 V
		2.2			V	4.5 V ≤ V <sub>DD1</sub> ≤ 6 V
Logic Low Input Voltage	V <sub>IL</sub>			0.9	V	V <sub>DD1</sub> ≥ 6 V
				0.85	V	4.5 V ≤ V <sub>DD1</sub> ≤ 6 V
Logic Input Hysteresis	V <sub>HYST</sub>		1.11		V	V <sub>DD1</sub> ≥ 6 V
			1.02		V	4.5 V ≤ V <sub>DD1</sub> ≤ 6 V
UVLO_FAULT						
Logic High Input Voltage	V <sub>IH_F</sub>	2.82			V	V <sub>DD1</sub> ≥ 6 V
		2.56			V	4.5 V ≤ V <sub>DD1</sub> ≤ 6 V
Logic Low Input Voltage	V <sub>IL_F</sub>			1.62	V	V <sub>DD1</sub> ≥ 6 V
				1.46	V	4.5 V ≤ V <sub>DD1</sub> ≤ 6 V
Logic Input Hysteresis	V <sub>HYS_F</sub>		0.93		V	V <sub>DD1</sub> ≥ 6 V
			0.84		V	4.5 V ≤ V <sub>DD1</sub> ≤ 6 V
MISO Logic Output						
MISO N Channel Field Effect Transistor (NFET) Drain to Source On Resistance (R <sub>DS(on)</sub> )	R <sub>DS(on)_MISO_N</sub>		9	20	Ω	MISO current (I <sub>MISO</sub> ) = 5 mA, V <sub>DD1</sub> = 4.5 V
MISO P Channel Field Effect Transistor (PFET) R <sub>DS(on)</sub>	R <sub>DS(on)_MISO_P</sub>		13	30	Ω	I <sub>MISO</sub> = 5 mA, V <sub>DD1</sub> = 4.5 V
MISO NFET High-Z Leakage	I <sub>MISO_LK_N</sub>	−0.1	+0.01	+0.1	μA	MISO = 0 V
MISO PFET High-Z Leakage	I <sub>MISO_LK_P</sub>	−0.1	+0.01	+0.1	μA	MISO = 5 V

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
UVLO						
Positive Going Threshold						
V <sub>DD1</sub>	V <sub>VDD1UV+</sub>		4.25	4.50	V	
V <sub>DD2</sub>	V <sub>VDD2UV+</sub>		11.57	11.72	V	
Negative Going Threshold						
V <sub>DD1</sub>	V <sub>VDD1UV-</sub>	4.0	4.17		V	
V <sub>DD2</sub>	V <sub>VDD2UV-</sub>	11.0	11.24		V	
Hysteresis						
V <sub>DD1</sub>	V <sub>VDD1UVH</sub>		0.1		V	
V <sub>DD2</sub>	V <sub>VDD2UVH</sub>		0.33		V	
PROTECTION FEATURES						
DRIVER_FAULT						
DRIVER_FAULT Pull-Up Current Source	I <sub>PU_DF</sub>	71	78	84	μA	Tested at 0 V
DRIVER_FAULT R <sub>DS(on)</sub>	R <sub>ON_DF</sub>		17	40	Ω	Tested at 20 mA, V <sub>DD1</sub> = 4.5 V
UVLO_FAULT						
UVLO_FAULT Pull-Up Current Source	I <sub>PU_UF</sub>	71	78	85	μA	Tested at 0 V
UVLO_FAULT R <sub>DS(on)</sub>	R <sub>ON_UF</sub>		14	34	Ω	Tested at 20 mA, V <sub>DD1</sub> = 4.5 V
FAULT						
FAULT P Type Metal-Oxide Semiconductor (PMOS)	R <sub>FLT_PMO5</sub>		4.18	8.35	Ω	Tested at 20 mA, V <sub>DD1</sub> = 4.5 V
FAULT N Type Metal-Oxide Semiconductor (NMOS)	R <sub>FLT_NMO5</sub>		5.11	10.15	Ω	Tested at 20 mA, V <sub>DD1</sub> = 4.5 V
Pull-Down	R <sub>FLT_PD</sub>	0.84	1.11	1.38	MΩ	
Low Gate Voltage						
Reference Voltage	V <sub>VL</sub>	9.68	9.92	10.11	V	V <sub>DD2</sub> = 15 V
Fault Delay Time	t <sub>DVL</sub>	11.18	12.73	14.67	μs	V <sub>DD2</sub> = 15 V
Fault Delay Time	t <sub>DVL_FLT</sub>	570	723	890	ns	To FAULT
	t <sub>DVL_DFLT</sub>	560	721	920	ns	To DRIVER_FAULT
	t <sub>DEL1</sub>	4740	6767	9700	ns	To UVLO_FAULT
Overcurrent						
Voltage						
Temperature Ramp Disabled	V <sub>OCD_TH</sub>	1.9	2	2.1	V	T_RAMP_OP = 1
Temperature Ramp Enabled	V <sub>OCD_TH_EN</sub>	2.59	2.7	2.8	V	T_RAMP_OP = 0, TS1 = 1.55 V
		1.85	1.96	2.1	V	T_RAMP_OP = 0, TS1 = 2.25 V
		1.65	1.75	1.82	V	T_RAMP_OP = 0, TS1 = 2.45 V
Hysteresis						
Temperature Ramp Disabled	V <sub>OCD_HYST</sub>		0.17		V	T_RAMP_OP = 1
Temperature Ramp Enabled	V <sub>OCD_HYST_EN</sub>		0.17		V	T_RAMP_OP = 0, TS1 = 1.55 V
			0.17		V	T_RAMP_OP = 0, TS1 = 2.25 V
			0.17		V	T_RAMP_OP = 0, TS1 = 2.45 V
OC1 Pull-Up Current Source	I <sub>OC1_PU</sub>	3.8	5	6.2	μA	
OC2 Pull-Up Current Source	I <sub>OC2_PU</sub>	3.8	5	6.2	μA	
Detect Delay Time	t <sub>dOC</sub>	650	787	936	ns	OC_2LEV_OP = 0, OC_TIME_OP = 0
Time to Report Overcurrent Fault to FAULT Pin	t <sub>REPORT</sub>	570	725	900	ns	OC_2LEV_OP = 1, to FAULT
		420	724	1020	ns	OC_2LEV_OP = 1, to DRIVER_FAULT
Detect Blanking	t <sub>BLANK</sub>	300	360	445	ns	t <sub>BLANK</sub> bits = 0001

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
ASC						
ASC Detect Comparator Voltage	$V_{ASC}$	8.43	8.93	9.34	V	ASC = 2 V
Hysteresis	$V_{ASC\_HYS}$		0.85		V	
Internal Current Source	$I_{ASC}$	130	153	178	$\mu A$	
ASC Filter	$t_{ASC\_F}$		53	104	ns	
Time to Report ASC	$t_{ASC}$	360	537	820	ns	
TSD						
Primary Side TSD						
Positive Edge	$t_{TSD\_POS1}$		154		$^{\circ}C$	
Negative Edge	$t_{TSD\_NEG1}$		135		$^{\circ}C$	
Secondary Side TSD						
Positive Edge	$t_{TSD\_POS2}$		150		$^{\circ}C$	
Negative Edge	$t_{TSD\_NEG2}$		130		$^{\circ}C$	
Isolated Temperature Sensor						
Temperature Sense						
Bias Current Source	$I_{T1}$	0.90	1.0	1.11	mA	TS1 = 2.2 V
	$I_{T2}$	0.92	1.0	1.12	mA	TS2 = 2.2 V
Matching	$I_{T\_MATCH}$		0.011	0.074	mA	TSx = 2.2 V
Pulse-Width Modulation (PWM)	$f_{PWM}$	9.3	10.0	10.7	kHz	PWM_OSC = 0, TSx = 2.25 V
Output Frequency		46.4	50.0	53.0	kHz	PWM_OSC = 1, TSx = 2.25 V
PWM Duty Cycle		8.1	10.2	11.4	%	PWM_OSC = 0, TSx = 2.45 V
		26.5	28.4	29.8	%	PWM_OSC = 0, TSx = 2.25 V
		90.6	92.1	93.5	%	PWM_OSC = 0, TSx = 1.55 V
		8.0	10.3	12.4	%	PWM_OSC = 1, TSx = 2.45 V
		26.1	28.5	30.9	%	PWM_OSC = 1, TSx = 2.25 V
		89.7	92.0	94.2	%	PWM_OSC = 1, TSx = 1.55 V
Duty Cycle						
Minimum		0.67	1.3	2.05	%	TS1 = 3.0 V
Maximum		98.5	99	99.2	%	TS1 = 0 V
Overtemperature						
Detect Delay Time	$t_{DOT}$	0.9	1.00	1.14	ms	
Fault Delay Time	$t_{DOT\_FLT}$	530	715	920	ns	
Detection Voltage						
Rising	$V_{OT\_0\_R}$	1.62	1.69	1.75	V	OT_FAULT_SEL = 0
	$V_{OT\_1\_R}$	1.67	1.73	1.79	V	OT_FAULT_SEL = 1
Falling	$V_{OT\_0\_F}$	1.59	1.64	1.70	V	OT_FAULT_SEL = 0
	$V_{OT\_1\_F}$	1.63	1.68	1.74	V	OT_FAULT_SEL = 1
Hysteresis	$V_{OT\_HYST\_0\_R}$		50		mV	OT_FAULT_SEL = 0
	$V_{OT\_HYST\_1\_R}$		50		mV	OT_FAULT_SEL = 1
Low Temperature Threshold						
Rising	$V_{LOW\_T\_R}$	2.33	2.40	2.46	V	TS1 pin voltage
Falling	$V_{LOW\_T\_F}$	2.32	2.36	2.40	V	TS1 pin voltage
Hysteresis	$V_{LOW\_HYST\_T\_F}$		40		mV	
TEMP_OUT Resistance						
NMOS $R_{DS(on)}$	$R_{TEMP\_N}$		12	25	$\Omega$	TEMP_OUT current ( $I_{TEMP\_OUT}$ ) = 20 mA, $V_{DD1}$ = 4.5 V
PMOS $R_{DS(on)}$	$R_{TEMP\_P}$		14	26	$\Omega$	$I_{TEMP\_OUT}$ = 20 mA, $V_{DD1}$ = 4.5 V
Pull-Down	$R_{TEMP\_PD}$	0.9	1	1.3	M $\Omega$	
Miller Clamp Voltage Threshold	$V_{MILLER}$	1.88	2.0	2.14	V	Referenced to GND <sub>2</sub>

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
Fault Reporting						
Latch Assert Time A	$t_{LA\_A}$	10	13	16	ms	
Latch Assert Time B	$t_{LA\_B}$	18	20	23	ms	
Latch Assert Time C	$t_{LA\_C}$	23	26	30	ms	
DRIVE SPECIFICATIONS						
Internal NFET						
On Resistance	$R_{DS(on)_N}$		0.51	0.95	$\Omega$	$V_{OUT\_OFF}$ current ( $I_{VOUT\_OFF}$ ) = 0.5 A, $V_{DD1} = 6\text{ V}$ , $V_{DD2} = 12\text{ V}$
On Resistance 2 Level	$R_{DS(on)_N\_2LEV}$		1.78	3.45	$\Omega$	$I_{VOUT\_OFF} = 0.1\text{ A}$ , $V_{DD1} = 6\text{ V}$ , $V_{DD2} = 12\text{ V}$
Internal PFET						
On Resistance	$R_{DS(on)_P}$		0.64	1.18	$\Omega$	$V_{OUT\_ON}$ current ( $I_{VOUT\_ON}$ ) = 0.5 A, $V_{DD1} = 6\text{ V}$ , $V_{DD2} = 12\text{ V}$
On Resistance 2 Level	$R_{DS(on)_P\_2LEV}$		2.04	3.90	$\Omega$	$I_{VOUT\_ON} = 0.1\text{ A}$ , $V_{DD1} = 6\text{ V}$ , $V_{DD2} = 12\text{ V}$
Miller Pull-Down NFET	$R_{DS(on)\_MILLER}$		4	10	$\Omega$	Miller current ( $I_{MILLER}$ ) = 10 mA
$V_{OFF\_SOFT} R_{DS(on)}$	$R_{DS(on)\_SOFT\_OFF}$		15	33	$\Omega$	$V_{OFF\_SOFT}$ current ( $I_{OFF\_SOFT}$ ) = 10 mA
Peak Current	$I_{PEAKIP}$		6		A	$V_{DD2} = 15\text{ V}$ , 2 $\Omega$ external resistance
Two-Level Plateau Voltage	$V_{2LEV}$	11.67	11.89	12.05	V	
SWITCHING SPECIFICATIONS						
Pulse Width <sup>1</sup>	PW	70			ns	$V_{DD2} = 15\text{ V}$ , $V_{OUT\_ON} = V_{OUT\_OFF}$ , no load
Propagation Delay						
Rising <sup>2</sup>	$t_{DLH}$	78	105	131	ns	$V_{DD2} = 15\text{ V}$ , $V_{OUT\_ON} = V_{OUT\_OFF}$ , no load
Falling <sup>2</sup>	$t_{DHL}$	83	107	137	ns	$V_{DD2} = 15\text{ V}$ , $V_{OUT\_ON} = V_{OUT\_OFF}$ , no load
Dead Time	$t_{DEXT}$	0.91	1.00	1.11	$\mu\text{s}$	

<sup>1</sup> The minimum pulse width is the shortest pulse width at which the specified timing parameter is guaranteed.

<sup>2</sup>  $t_{DLH}$  propagation delay is measured from the time of the input rising logic high threshold,  $V_{IH}$ , to the output rising 0% level of the  $V_{OUT\_ON}$  or  $V_{OUT\_OFF}$  signal.  $t_{DHL}$  propagation delay is measured from the input falling logic low threshold,  $V_{IL}$ , to the output falling 90% threshold of the  $V_{OUT\_ON}$  or  $V_{OUT\_OFF}$  signal. See Figure 13 for waveforms of propagation delay parameters.

## SPI TIMING SPECIFICATIONS

SPI timing specifications are guaranteed by design. All devices are production tested with 200 kHz SPI communication.

Table 2.

Parameter	Description	Min	Typ	Max	Unit
$t_s$	Time to first clock edge	8			$\mu s$
$t_{DS}$	Set period	1			$\mu s$
$t_{DH}$	Hold period	1			$\mu s$
$t_{CLK}$	Clock period	5			$\mu s$
$t_H$	Release time	8			$\mu s$
$t_{HIGH}$	Clock time high	100			ns
$t_{LOW}$	Clock time low	100			ns
$t_{OV}$	Output valid time			240	ns

### SPI Timing Diagram

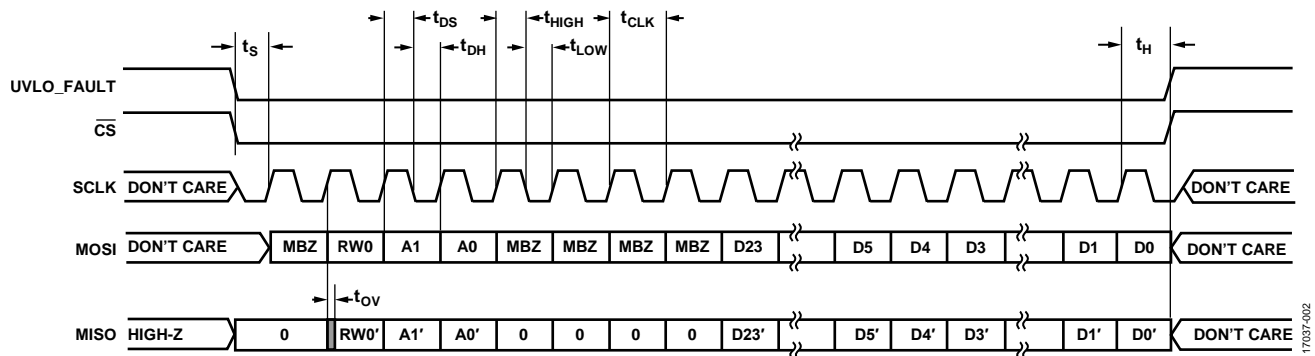


Figure 2. SPI Timing Diagram

## PACKAGE CHARACTERISTICS

Table 3.

Parameter	Symbol	Min	Typ	Max	Unit	Test Conditions/Comments
Resistance (Input Side to High-Side Output) <sup>1</sup>	$R_{I-O}$		$10^{12}$		$\Omega$	
Capacitance (Input Side to High-Side Output) <sup>1</sup>	$C_{I-O}$		2.0		pF	
Input Capacitance	$C_I$		4.0		pF	

<sup>1</sup> The device is considered a 2-terminal device: Pin 1 through Pin 14 are shorted together, and Pin 15 through Pin 28 are shorted together.



## REGULATORY INFORMATION

Table 4.

UL (Pending)	CSA (Pending)	VDE (Pending)	CQC (Pending)
UL 1577 Component Recognition Program Single Protection, 5000 V rms Isolation Voltage	Approved under CSA Component Acceptance Notice 5A CSA 60950-1-07+A1+A2 and IEC 60950-1, second edition, +A1+A2: Basic insulation at 830 V rms (1174 V <sub>PEAK</sub> ) Reinforced insulation at 415 V rms (587 V <sub>PEAK</sub> ) IEC 60601-1 Edition 3.1: Basic insulation (1 means of patient protection (MOPP)), 519 V rms (734 V <sub>PEAK</sub> ) Reinforced insulation (2 MOPP), 261 V rms (369 V <sub>PEAK</sub> ) CSA 61010-1-12 and IEC 61010-1 third edition Basic insulation, 300 V rms mains, 830 V secondary (1174 V <sub>PEAK</sub> ) Reinforced insulation, 300 V rms mains, 415 V secondary (587 V <sub>PEAK</sub> )	DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 Reinforced insulation at 849 V <sub>PEAK</sub> , V <sub>IOTM</sub> = 8 kV <sub>PEAK</sub>	Certified under CQC11-471543-2012 GB4943.1-2011  Basic insulation, 830 V rms (1174 V <sub>PEAK</sub> ) Reinforced insulation, 415 V rms (587 V <sub>PEAK</sub> )
File E214100	File 205078	File 2471900-4880-0001	File (pending)

## INSULATION AND SAFETY RELATED SPECIFICATIONS

Table 5.

Parameter	Symbol	Value	Unit	Test Conditions/Comments
Rated Dielectric Insulation Voltage		5000	V rms	1 minute duration
Minimum External Air Gap (Clearance)	L (I01)	8.3	mm min	Measured from input terminals to output terminals, shortest distance through air
Minimum External Tracking (Creepage)	L (I02)	8.3	mm min	Measured from input terminals to output terminals, shortest distance path along body
Minimum Clearance in the Plane of the Printed Circuit Board (PCB Clearance)	L (PCB)	8.7	mm min	Measured from input terminals to output terminals, shortest distance through air, line of sight, in the PCB mounting plane
Minimum Internal Gap (Internal Clearance)		0.017	mm min	Insulation distance through insulation
Tracking Resistance (Comparative Tracking Index)	CTI	>400	V	DIN IEC 112/VDE 0303 Part 1
Material Group		II		Material group (DIN VDE 0110, 1/89, Table 1)

**DIN V VDE V 0884-10 (VDE V 0884-10) INSULATION CHARACTERISTICS**

These isolators are suitable for reinforced isolation only within the safety limit data. Maintenance of the safety data is ensured by protective circuits. The asterisk (\*) marking on the package denotes DIN V VDE V 0884-10 approval for a 560 V<sub>PEAK</sub> working voltage.

**Table 6. VDE Characteristics**

Description	Test Conditions/Comments	Symbol	Characteristic	Unit
Installation Classification per IEC 60664-1			I to IV	
For Rated Mains Voltage ≤ 150 V rms			I to IV	
For Rated Mains Voltage ≤ 300 V rms			I to IV	
For Rated Mains Voltage ≤ 600 V rms			40/125/21	
Climatic Classification			2	
Pollution Degree per DIN VDE 0110, Table 1				
Maximum Working Insulation Voltage		V <sub>IORM</sub>	849	V <sub>PEAK</sub>
Input to Output Test Voltage, Method B1	V <sub>IORM</sub> × 1.875 = V <sub>pd(m)</sub> , 100% production test, t <sub>ini</sub> = t <sub>m</sub> = 1 sec, partial discharge < 5 pC	V <sub>pd(m)</sub>	1592	V <sub>PEAK</sub>
Input to Output Test Voltage, Method A	V <sub>IORM</sub> × 1.5 = V <sub>pd(m)</sub> , t <sub>ini</sub> = 60 sec, t <sub>m</sub> = 10 sec, partial discharge < 5 pC	V <sub>pd(m)</sub>		
After Environmental Tests Subgroup 1			1274	V <sub>PEAK</sub>
After Input and/or Safety Test Subgroup 2 and Subgroup 3	V <sub>IORM</sub> × 1.2 = V <sub>pd(m)</sub> , t <sub>ini</sub> = 60 sec, t <sub>m</sub> = 10 sec, partial discharge < 5 pC		1019	V <sub>PEAK</sub>
Highest Allowable Overvoltage Impulse		V <sub>IOTM</sub>	8000	V <sub>PEAK</sub>
	1.2 μs rise time, 50 μs, 50% fall time in air to the preferred sequence	V <sub>IMPULSE</sub>	8000	V <sub>PEAK</sub>
Surge Isolation Voltage Basic	V <sub>PEAK</sub> = 12.8 kV, 1.2 μs rise time, 50 μs, 50% fall time	V <sub>IOSM</sub>	9800	V <sub>PEAK</sub>
Surge Isolation Voltage Reinforced	V <sub>PEAK</sub> = 12.8 kV, 1.2 μs rise time, 50 μs, 50% fall time	V <sub>IOSM</sub>	8000	V <sub>PEAK</sub>
Safety Limiting Values	Maximum value allowed in the event of a failure (see Figure 3)			
Maximum Junction Temperature		T <sub>s</sub>	150	°C
Total Power Dissipation at T <sub>A</sub> = 25°C		P <sub>s</sub>	2.0	W
Insulation Resistance at T <sub>s</sub>	Voltage between the input and output (V <sub>io</sub> ) = 500 V	R <sub>s</sub>	>10 <sup>9</sup>	Ω

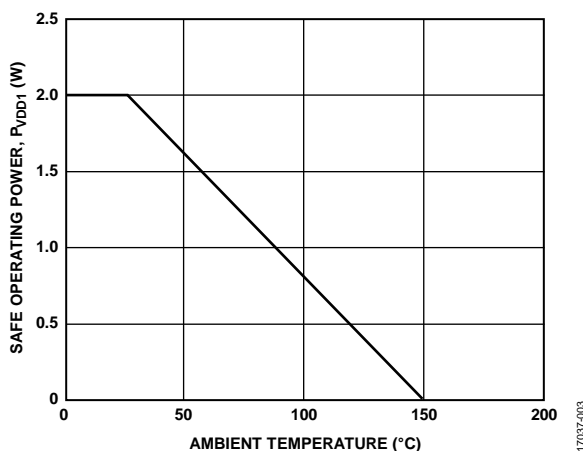


Figure 3. Thermal Derating Curve, Dependence of Safety Limiting Values on Ambient Temperature, per DIN V VDE V 0884-10

**RECOMMENDED OPERATING CONDITIONS****Table 7.**

Parameter	Value
Operating Temperature Range (T <sub>A</sub> )	−40°C to +125°C
Supply Voltages	
V <sub>DD1</sub> <sup>1</sup>	4.5 V to 25 V
V <sub>DD2</sub> <sup>2</sup>	12 V to 25 V

<sup>1</sup> Referenced to GND<sub>1</sub>.

<sup>2</sup> Referenced to GND<sub>2</sub>.

## ABSOLUTE MAXIMUM RATINGS

Table 8.

Parameter	Rating
Storage Temperature Range ( $T_{ST}$ )	–55°C to +150°C
Junction Operating Temperature Range ( $T_J$ )	–40°C to +150°C
Supply Voltages	
$V_{DD1}^1$	–0.2 V to +30 V
$V_{DD2}^2$	–0.2 V to +30 V
Primary Side Pins <sup>1</sup>	
VI+, VI–, MOSI, $\overline{CS}$ , SCLK	–0.2 V to +5.5 V
$\overline{FAULT}$ , TEMP_OUT, MISO, DRIVER_ $\overline{FAULT}$ , UVLO_ $\overline{FAULT}$	–0.2 V to $V_{5\_1} + 0.2$ V
Secondary Side Pins <sup>2</sup>	
TS1, TS2	–0.2 V to $V_{5\_2} + 0.2$ V
MILLER_OUT, $V_{OFF\_SOFT}$ , $V_{OUT\_OFF}$	–0.2 V to +30 V
GATE_SENSE, OC1, OC2	–0.2 V to $V_{DD2} + 0.2$ V
$V_{OUT\_ON}$ , ASC	–0.2 V to $V_{DD2} + 0.2$ V
Common-Mode Transients ( $ CM $ )	–150 kV/ $\mu$ s to +150 kV/ $\mu$ s

<sup>1</sup> Referenced to GND<sub>1</sub>.<sup>2</sup> Referenced to GND<sub>2</sub>.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

## THERMAL RESISTANCE

Thermal performance is directly linked to PCB design and operating environment. Careful attention to PCB thermal design is required.

$\theta_{JA}$  is the junction to ambient thermal resistance, and  $\Psi_{JT}$  is the junction to top characterization parameter.

Table 9. Thermal Resistance

Package Type <sup>1</sup>	$\theta_{JA}$	$\Psi_{JT}$	Unit
RN-28-1	62.4	2.97	°C/W

<sup>1</sup> 4-layer PCB.

## ESD CAUTION



**ESD (electrostatic discharge) sensitive device.** Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

Table 10. Maximum Continuous Working Voltage<sup>1, 2, 3</sup>

Parameter	Rating	Constraint
AC Voltage		
Bipolar Waveform		
Basic Insulation	849 V <sub>PEAK</sub>	Lifetime limited by insulation lifetime per VDE-0884-11
Reinforced Insulation	707 V <sub>PEAK</sub>	Lifetime limited by insulation lifetime per VDE-0884-11
Unipolar Waveform		
Basic Insulation	1697 V <sub>PEAK</sub>	Lifetime limited by insulation lifetime per VDE-0884-11
Reinforced Insulation	892 V <sub>PEAK</sub>	Lifetime limited by package creepage per IEC 60664-1
DC Voltage		
Basic Insulation	1092 V <sub>PEAK</sub>	Lifetime limited by package creepage per IEC 60664-1
Reinforced Insulation	546 V <sub>PEAK</sub>	Lifetime limited by package creepage per IEC 60664-1

<sup>1</sup> See the Insulation Lifetime section for details.<sup>2</sup> Other pollution degree and material group requirements yield a different limit.<sup>3</sup> Some system level standards allow components to use the printed wiring board (PWB) creepage values. The supported dc voltage may be higher for those standards.

Table 11. Truth Table (Positive Logic)<sup>1</sup>

VI+ Input	VI- Input	ASC	FAULT	DRIVER_FAULT	UVLO_FAULT	V <sub>DD1</sub> State	V <sub>DD2</sub> State	V <sub>OFF_SOFT</sub>	V <sub>OUT_ON</sub>	V <sub>OUT_OFF</sub>
Low	High	<9 V	High	High	High	Powered	Powered	Low	Low	High
High	Low	<9 V	High	High	High	Powered	Powered	Low	High	Low
High	High	<9 V	High	High	High	Powered	Powered	Low	Low	High
Low	Low	<9 V	High	High	High	Powered	Powered	Low	Low	High
X	X	>9 V	High	Low	High	Powered	Powered	Low	High	Low
X	X	X	Low	X	X	Powered	Powered	High	X	Low <sup>3</sup>
X	X	X	X	Low	X	Powered	Powered	High <sup>3,4</sup>	X	X
X	X	X	X	X	Low	Powered	Powered	High <sup>3</sup>	X	X
X	X	>9 V	X	X	X	Unpowered	Powered	Low	High	Low
X	X	<9 V	X	X	X	Unpowered	Powered	Low	Low	High
X	X	X	X	X	X	X	Unpowered	High-Z	High-Z	Low <sup>2</sup>

<sup>1</sup> X means don't care or unknown.<sup>2</sup> With an unpowered V<sub>DD2</sub>, the ADuM4137 tries to hold the IGBT gate voltage to a value of approximately 3 V to 5 V.<sup>3</sup> The NMOS on V<sub>OUT\_OFF</sub> is off during soft shutdown until the GATE\_SENSE pin reaches 2 V, then the V<sub>OUT\_OFF</sub> NMOS turns on along with the Miller clamp.<sup>4</sup> The driver only goes into soft shutdown when an actual fault occurs, such as an overcurrent, gate low violation or an error correction code (ECC) error (see Table 12 for fault mapping).

Table 12. FAULT Pin Mapping

Fault Conditions	FAULT Pin	DRIVER_FAULT Pin	UVLO_FAULT Pin
TSD	Low, Latch Assert Time B = 20 ms (typical)	Don't care or unknown	Don't care or unknown
TSx_OT_FAULT	Low, Latch Assert Time B = 20 ms (typical)	Don't care or unknown	Don't care or unknown
Gate Low	Low, Latch Assert Time C = 26 ms (typical)	Low, Latch Assert Time C = 26 ms (typical)	Low, Latch Assert Time C = 26 ms (typical)
V <sub>DD2</sub> UVLO	Low, Latch Assert Time B = 20 ms (typical)	Don't care or unknown	Low, Latch Assert Time A = 13 ms (typical)
OCx Overcurrent	Low, Latch Assert Time B = 20 ms (typical)	Low, Latch Assert Time C = 26 ms (typical)	Don't care or unknown
ECC Error	Low, Latch Assert Time B = 20 ms (typical)	Low, Latch Assert Time C = 26 ms (typical)	Don't care or unknown
ASC	Don't care or unknown	Low, Latch Assert Time C = 26 ms (typical)	Don't care or unknown
DT_FAULT	Don't care or unknown	Low, Latch Assert Time A = 13 ms (typical)	Don't care or unknown

## PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

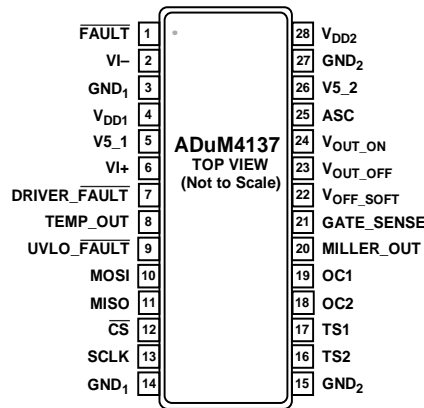


Figure 4. Pin Configuration

Table 13. Pin Function Descriptions

Pin No.	Mnemonic	Description
1	FAULT	Fault Reporting Pin. When FAULT is low, the driver is disabled for as long as the FAULT pin persists or for the extent of the latch time, whichever is longer. See Table 11 for the FAULT reporting truth table.
2	VI-	Inverting Input with Dead Time Control.
3	GND <sub>1</sub>	Ground Reference for the Primary Side.
4	V <sub>DD1</sub>	Input Supply Voltage on the Primary Side, 4.5 V to 25 V Referenced to GND <sub>1</sub> .
5	V5_1	5 V Regulated Output. Connect this pin to a 1 $\mu$ F external capacitor referenced to GND <sub>1</sub> . This pin controls logic levels for the input pins.
6	VI+	Noninverting Input.
7	DRIVER_FAULT	Fault Reporting Pin. When an OCx fault, gate low fault, ECC fault, an ASC event, or DT_FAULT occurs, the DRIVER_FAULT pin is driven low on the primary side.
8	TEMP_OUT	10 kHz or 50 kHz, 1.3% to 99% (Typical) PWM Output for Diode Temperature Sensor.
9	UVLO_FAULT	UVLO_FAULT Fault Reporting Pin. See Table 11 for the FAULT reporting truth table. When the UVLO_FAULT pin is pulled low externally, the SPI interface is activated.
10	MOSI	MOSI Connection for SPI Bus.
11	MISO	MISO Connection for SPI Bus.
12	CS	Chip Select for SPI Bus.
13	SCLK	Clock for SPI Bus.
14	GND <sub>1</sub>	Ground Reference for the Primary Side.
15	GND <sub>2</sub>	Ground Reference for the Secondary Side.
16	TS2	Remote Temperature Sensor 2. Float or pull high to V5_2 if not used.
17	TS1	Remote Temperature Sensor 1. See the Applications Information section for more information if unused.
18	OC2	Split Emitter Overcurrent Detection 2. Connect this pin to GND <sub>2</sub> if not used.
19	OC1	Split Emitter Overcurrent Detection 1. Connect this pin to GND <sub>2</sub> if not used.
20	MILLER_OUT	Output Signal to Control External MOSFET for Miller Clamping.
21	GATE_SENSE	Miller Clamp Sense Pin. Connect this pin directly to the gate of the IGBT.
22	V <sub>OFF_SOFT</sub>	Soft Shutdown Gate Connection. Connect this pin to the gate through the external series resistor. This pin pulls the gate down during fault conditions.
23	V <sub>OUT_OFF</sub>	Turn Off Current Path Connection. Connect this pin to the gate through an external series resistor. This pin pulls the gate down during a low output command.
24	V <sub>OUT_ON</sub>	Turn On Current Path Connection. Connect this pin to the gate through an external series resistor. This pin pulls the gate up during a high output command.
25	ASC	External Secondary Side Control for Enabling the Driver. The ASC pin has a comparator triggering at 8.93 V (typical) with 0.85 V (typical) of hysteresis. When the ASC signal is greater than 8.93 V (typical), the pin forces the driver on if no fault occurs.
26	V5_2	5 V Regulated Output on the Secondary Side. Connect this pin to a 1 $\mu$ F external capacitor referenced to GND <sub>2</sub> .
27	GND <sub>2</sub>	Ground Reference for the Secondary Side.
28	V <sub>DD2</sub>	Input Supply Voltage on the Secondary Side, Referenced to GND <sub>2</sub> .

## TYPICAL PERFORMANCE CHARACTERISTICS

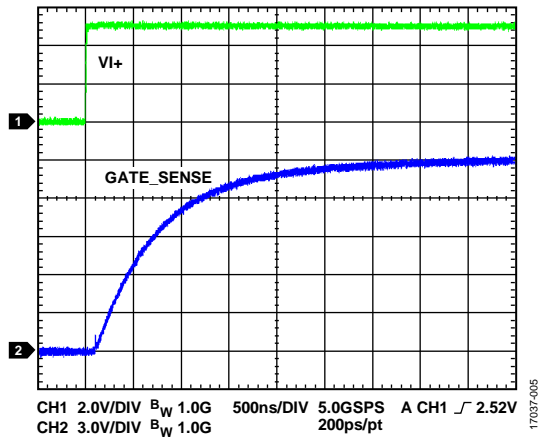


Figure 5. Example Turn On Edge,  $V_{DD1} = 5\text{ V}$ ,  $V_{DD2} = 15\text{ V}$ ,  $3\Omega$  Turn On,  $100\text{ nF}$  Load

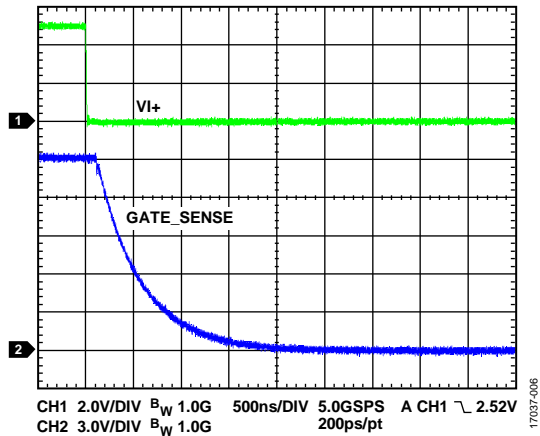


Figure 6. Example Turn Off Edge,  $V_{DD1} = 5\text{ V}$ ,  $V_{DD2} = 15\text{ V}$ ,  $2\Omega$  Turn Off,  $100\text{ nF}$  Load

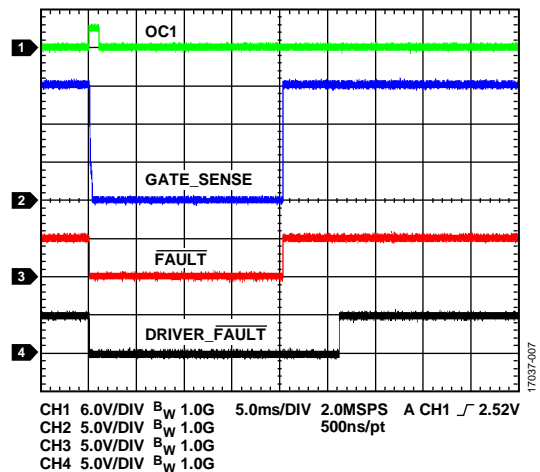


Figure 7. Example Overcurrent Fault,  $V_{DD1} = 5\text{ V}$ ,  $V_{DD2} = 15\text{ V}$ ,  $VI+ = 5\text{ V}$ ,  $1\text{ ms}$  Overcurrent Simulation,  $100\text{ nF}$  Load

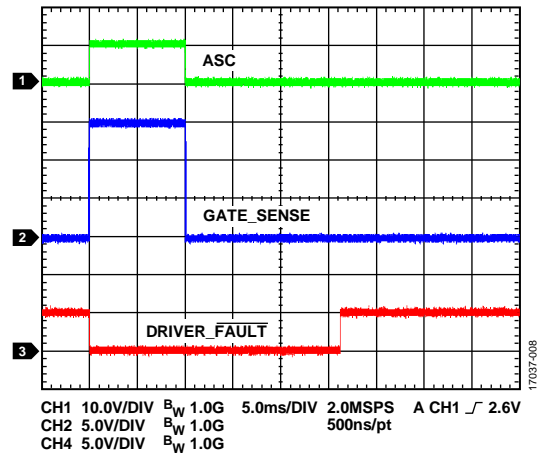


Figure 8. Example ASC Signal,  $V_{DD1} = 5\text{ V}$ ,  $V_{DD2} = 15\text{ V}$ ,  $VI+ = 5\text{ V}$ ,  $10\text{ ms}$  ASC,  $100\text{ nF}$  Load

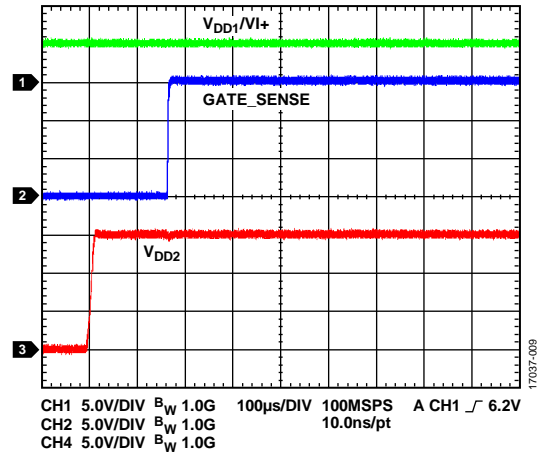


Figure 9. Typical  $V_{DD2}$  Startup Time,  $VI+ = V_{DD1}$

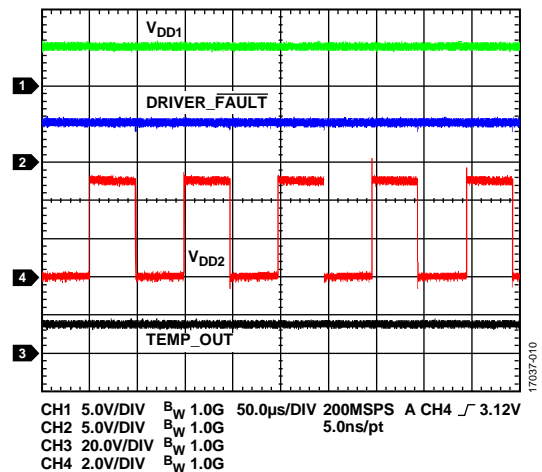


Figure 10. Example  $TEMP\_OUT$  Reading,  $V_{DD1} = 5\text{ V}$ ,  $V_{DD2} = 15\text{ V}$ ,  $2\text{ k}\Omega$  Resistor on TS1

## THEORY OF OPERATION

Gate drivers are required in situations where fast rise times of switching device gates are required. The gate signals for enhancement power devices are referenced to a source or emitter node. The gate driver must follow this source or emitter node. As such, isolation is necessary between the controlling signal and the output of the gate driver in topologies where the source or emitter nodes swing, such as a half bridge. Gate switching times are a function of the drive strength of the gate driver. Buffer stages before a complementary metal-oxide semiconductor (CMOS) output reduce the total delay time and increase the final drive strength of the driver.

The ADuM4137 achieves isolation between the control side and the output side of the gate driver using a high frequency carrier that transmits data across the isolation barrier with *iCoupler*

chip scale transformer coils separated by layers of polyimide isolation. The ADuM4137 uses positive logic on/off keying (OOK) encoding, in which a high signal is transmitted by the presence of the carrier frequency across the *iCoupler* chip scale transformer coils. Positive logic encoding ensures that a low signal is seen on the output when the input side of the gate driver is unpowered. A low state is the most common safe state in enhancement mode power devices and can drive in situations where shoot through conditions are present. The architecture of the ADuM4137 is designed for high common-mode transient immunity and high immunity to electrical noise and magnetic interference. Radiated emissions are minimized with a spread spectrum OOK carrier and differential coil layout. Figure 11 shows the OOK encoding used by the ADuM4137.

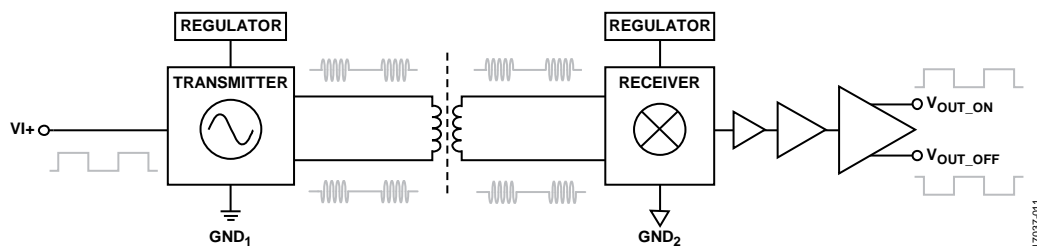


Figure 11. Operational Block Diagram of OOK Encoding

## APPLICATIONS INFORMATION

### PCB LAYOUT

The ADuM4137 IGBT gate driver requires no external interface circuitry for the logic interfaces. Power supply bypassing is required at the  $V_{DD1}$  and  $V_{DD2}$  supply pins. Use a ceramic capacitor  $>10\ \mu\text{F}$  on  $V_{DD1}$  to  $\text{GND}_1$ . Add at least  $30\ \mu\text{F}$  to  $60\ \mu\text{F}$  of capacitance on the output power supply pin ( $V_{DD2}$ ) to provide the charge required to drive the gate capacitance at the outputs. This capacitance can be provided by multiple parallel capacitors. Avoid using vias on the bypass capacitor or employ multiple vias to reduce the inductance in the bypassing because board vias can introduce parasitic inductance. The total lead length between both ends of the smaller capacitor and the input or output power supply pin must not exceed approximately 5 mm. For the 5 V regulators, place  $1\ \mu\text{F}$  capacitors as close as possible to the ADuM4137.

To improve robustness against bulk current injection, the input pins ( $\text{VI}+$ ,  $\text{VI}-$ , MOSI,  $\overline{\text{CS}}$ , and SCLK) can have series  $100\ \Omega$  resistors placed to limit current. The inclusion of  $100\ \Omega$  resistors in series with input lines is highly recommended.

### SPI AND EEPROM OPERATION

#### *SPI Programming*

The ADuM4137 contains an SPI bus for setting remote temperature gains and offsets, PWM reporting frequency, high temperature faults, and low temperature operation mode.

SPI programming is enabled when  $\overline{\text{CS}}$  is low and  $\text{UVLO\_FAULT}$  is actively pulled low. The SPI bus allows programming of the secondary side EEPROM, allowing a permanent operation setting. The SPI interface can operate in a daisy-chain mode to allow efficient use of the microcontroller input and output pins. When used in a daisy-chain configuration, the ADuM4137 expects an integer multiple of 24 clock cycles for each chip select. All noninteger multiples of 24 clock cycles within a chip select period are ignored. If the ADuM4137 is in a daisy-chain link with devices other than ADuM4137 devices, ensure that the register space of the other devices adds up to an integer multiple of 24. When the chip select pin ( $\overline{\text{CS}}$ ) is brought low while the  $\text{UVLO\_FAULT}$  pin is pulled low, programming of the EEPROM is available. However, the gate drive output is disabled. The gate drive output is available again when  $\overline{\text{CS}}$  is brought back to high.

Programming is performed using the standard SPI convention of clock polarity,  $\text{CPOL} = 0$  and clock phase  $\text{CPHA} = 1$ . The timing diagram in Figure 2 demonstrates a typical read or write operation. Bit A1 and Bit A0 are the address bits. The must be zero (MBZ) bits must be set to 0. Bits[D23:D0] are the data bits, with MSB first. Bit RW0 sets whether the action is a read (0) or a write (1).



## USER REGISTER MAP

Figure 12 shows the user trim register map and binary addresses.

ADDRESS	NAME	BIT																								
		23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0	
00	USER	OFFSET_2[5:0]						GAIN_2[5:0]						OFFSET_1[5:0]						GAIN_1[5:0]						
01	CONFIG	RESERVED								OT_FAULT_OP	OT_FAULT_SEL	OC_TIME_OP	OC_2LEV_OP	LOW_T_OP	OC_BLANK_OP	t <sub>BLANK</sub> [3:0]			ECC_OFF_OP	RESERVED				T_RAMP_OP	PWM_OSC	
10	CONTROL	RESERVED																		ECC2_DBL_ERR		ECC2_SNG_ERR	ECC1_DBL_ERR	ECC1_SNG_ERR	PROG_BUSY	SIM_TRIM

17037-012

Figure 12. User Trim Register Map

### USER REGISTER BITS

Table 14 lists the user register (Address 00) bits and bit descriptions.

Table 14. User Register (Address 00) Bit Descriptions

Bit(s)	Bit Name	Description
[23:18]	OFFSET_2[5:0]	TS2 offset
[17:12]	GAIN_2[5:0]	TS2 gain
[11:6]	OFFSET_1[5:0]	TS1 offset
[5:0]	GAIN_1[5:0]	TS1 gain

#### OFFSET\_2[5:0] Bits

Use the OFFSET\_2 bits of the EEPROM to adjust the internal offset for the TS2 pin. See the Isolated Temperature Sensor section for more information.

#### GAIN\_2[5:0] Bits

Use the GAIN\_2 bits of the EEPROM to adjust the internal gain for the TS2 pin. See the Isolated Temperature Sensor section for more information.

#### OFFSET\_1[5:0] Bits

Use the OFFSET\_1 bits of the EEPROM to adjust the internal offset for the TS1 pin. See the Isolated Temperature Sensor section for more information.

#### GAIN\_1[5:0] Bits

Use the GAIN\_1 bits of the EEPROM to adjust the internal gain for the TS1 pin. See the Isolated Temperature Sensor section for more information.

### CONFIGURATION REGISTER BITS

Table 15 lists the configuration (CONFIG) register (Address 01) bits and bit descriptions.

Table 15. CONFIG Register (Address 01) Bit Descriptions

Bit(s)	Bit Name	Description
[23:17]	Reserved	Reserved
16	OT_FAULT_OP	Overtemperature fault disable
15	OT_FAULT_SEL	Overtemperature fault select
14	OC_TIME_OP	Disable two-level drive and timer during overcurrent event
13	OC_2LEV_OP	Overcurrent two-level operation select
12	LOW_T_OP	Low temperature operation select
11	OC_BLANK_OP	Overcurrent blanking operation select
[10:7]	t <sub>BLANK</sub>	Overcurrent blanking time
6	ECC_OFF_OP	Enable soft shutdown with ECC fault
[5:2]	Reserved	Reserved
1	T_RAMP_OP	Overcurrent temperature ramp enable
0	PWM_OSC	Temperature reading output oscillator select

#### OT\_FAULT\_OP Bit

Set the OT\_FAULT\_OP bit to 1 to disable a fault for over-temperature. If this bit is set to 0, the ADuM4137 issues a fault when the TS1 or TS2 pin detects an overtemperature event.

#### OT\_FAULT\_SEL Bit

The OT\_FAULT\_SEL bit selects between two overtemperature fault voltage thresholds. Set this bit to 0 to set the falling threshold to 1.64 V (typical) and the rising threshold is 1.69 V (typical). Set the OT\_FAULT\_SEL bit to 1 to set the falling threshold to 1.68 V (typical) and the rising threshold is 1.73 V (typical).

**OC\_TIME\_OP Bit**

Set the OC\_TIME\_OP bit to 1 to disable the two-level drive and timer during an overcurrent event. During an overcurrent event, the output immediately enters soft shutdown. If enabled, overcurrent blanking is still available.

**OC\_2LEV\_OP Bit**

Set the OC\_2LEV\_OP bit to 1 to disable the two-level drive during an overcurrent event before a fault registers. After the overcurrent detection time completes, a fault register and the output shuts down using soft shutdown. If this bit is set to 0 during an overcurrent event, but before  $t_{dOC}$ , the two-level drive level is output to the gate.

**LOW\_T\_OP Bit**

Bit 12 of the CONFIG register can disable a special low temperature operation. If the LOW\_T\_OP bit is set to 0 when the TS1 pin rises above 2.40 V (typical), the gate voltage goes to the two-level plateau voltage during an on command. Hysteresis allows operation down to 2.36 V (typical) on TS1 before the low temperature operation mode is exited. If the LOW\_T\_OP bit is set to 1, all nonfault gate signals are at the  $V_{DD2}$  output voltage on an on signal.

**OC\_BLANK\_OP Bit**

Set OC\_BLANK\_OP to 1 to enable two-level drive during current blanking time. When the OC\_BLANK\_OP bit is set to 1, it enters two-level drive in case of an overcurrent event during the blanking time,  $t_{BLANK}$ .

 **$t_{BLANK}[3:0]$  Bits**

During the initial turn on of a gate, a large amount of noise caused by switching actions can exist. By setting different  $t_{dOC}$  values, the overcurrent detection can be masked by setting different  $t_{BLANK}$  values. During the masking time, overcurrent events are ignored.

**Table 16.  $t_{BLANK}$  Blanking Times**

$t_{BLANK}[3:0]$ , Bits[10:7]	Blanking Time ( $\mu$ s) Typical
0000	0
0001	0.36
0010	0.56
0011	0.77
0100	0.97
0101	1.17
0110	1.57
0111	1.97
1000	2.37
1001	2.78
1010	3.18
1011	3.58
1100	3.98
1101	4.39
1110	4.79
1111	5.19

**ECC\_OFF\_OP Bit**

If the ECC\_OFF\_OP bit is set to 1 when an ECC error is detected, the ADuM4137 enters soft shutdown and a fault registers. This fault registers whether a single or double ECC fault is detected. If this bit is set to 0, ECC faults are set in the control register (Address 10), but the ADuM4137 continues to operate without shutting down.

**T\_RAMP\_OP Bit**

Set the T\_RAMP\_OP bit to 0 to allow the overcurrent reference voltage to vary with temperature. The current reference varies from 2.7 V (typical) to 1.75 V (typical) across the TS1 voltages of 1.55 V to 2.45 V, as shown in Figure 14. Set the T\_RAMP\_OP bit to 1 to have the overcurrent reference voltage,  $V_{OCD\_TH}$ , set to 2 V (typical) regardless of the sensed temperature.

**PWM\_OSC**

The PWM\_OSC bit controls whether the reported TEMP\_OUT pin PWM frequency is 10 kHz or 50 kHz. When the PWM\_OSC bit is set to 0, the output frequency is 10 kHz (typical). When the PWM\_OSC bit is set to 1, the PWM output frequency is 50 kHz (typical).

**CONTROL REGISTER BITS**

Table 17 lists the control register (Address 10) bits and bit descriptions.

**Table 17. Control Register (Address 10) Bit Descriptions**

Bit(s)	Bit Name	Description
[23:6]	Reserved	Reserved.
5	ECC2_DBL_ERR	ECC Bank 2 double error detected
4	ECC2_SNG_ERR	ECC Bank 2 single error detected
3	ECC1_DBL_ERR	ECC Bank 1 double error detected
2	ECC1_SNG_ERR	ECC Bank 1 single error detected
1	PROG_BUSY	Program/busy bit
0	SIM_TRIM	Simulate trim

**ECC2\_DBL\_ERR Bit**

When two errors are detected in the EEPROM stored data, the ECC2\_DBL\_ERR bit sets to 1 when read. Two errors are detectable. However, these errors cannot be corrected using the error correcting code employed by the ADuM4137. The ECC2\_DBL\_ERR bit set to 1 indicates when a double error is detected in the memory banks, representing trim performed on the ADuM4137 outside of registers affected by user and CONFIG addresses. When this bit is set to 0, it indicates no error was detected for bits greater than 1.

**ECC2\_SNG\_ERR Bit**

When a single error is detected in the EEPROM stored data, the ECC2\_SNG\_ERR bit sets to 1 when read. The error correcting code employed by the ADuM4137 can detect and correct a single error. The ECC2\_SNG\_ERR bit set to 1 indicates when a single error is detected in the memory banks, representing trim performed on the ADuM4137 outside of the registers affected by the user and configuration addresses. When this bit is set to 0, it indicates no single bit error was detected.

**ECC1\_DBL\_ERR Bit**

When two errors are detected in the EEPROM stored data, the ECC1\_DBL\_ERR bit sets to 1 when read. Two errors are detectable. However, these errors cannot be corrected using the error correcting code employed by the ADuM4137. The ECC2\_DBL\_ERR bit set to 1 indicates that a double error is detected in the memory banks, representing trim performed on the ADuM4137 by the user and configuration addresses. A value of 0 indicates no error was detected for bits greater than 1.

**ECC1\_SNG\_ERR Bit**

When a single error is detected in the EEPROM stored data, the ECC1\_SNG\_ERR bit is set to 1 when read. The error correcting code employed by the ADuM4137 can detect and correct a single error. The ECC2\_SNG\_ERR bit set to 1 indicates that a single error is detected in the memory banks, representing trim performed on the ADuM4137 by the user and configuration addresses. A value of 0 indicates no single bit error was detected.

**PROG\_BUSY Bit**

Set the PROG\_BUSY bit high to program the EEPROM memory. When this bit is set to 1, the EEPROM begins to write to the memory. The hardware sets this bit back to 0 to indicate that programming has occurred. The write sequence takes 40 ms (maximum) to perform but can write faster than 40 ms (maximum). If a shorter wait time is required, read the PROG\_BUSY bit back multiple times during the write time. If 0 is read back after the user sets the bit to 1, the write completes.

**SIM\_TRIM Bit**

If the SIM\_TRIM bit is set to 0, the user and configuration registers have no effect on the operation of the ADuM4137. Use this bit to simulate trim settings but not to write to the registers.

If SIM\_TRIM is set high, address values can change the operation of the gate driver to simulate the effect of programming the values to the EEPROM across power-ups. When SIM\_TRIM is set to 0, previous address values from the EEPROM are loaded, and operation returns to the power on state.

**SPI SAFETY**

To reduce single-point failure nodes, bring two signals low to activate the SPI communication. During SPI communication, the forward path channel deactivates. To activate SPI communication, drive both the UVLO\_FAULT pin and CS pins low. Pull the UVLO\_FAULT pin low using an external open-drain connection to not disrupt the normal UVLO\_FAULT behavior. When the UVLO\_FAULT pin is high, the SPI is not active. Refer to Table 12 for the FAULT pin mapping. For normal operation, a FAULT (TSD, TSx\_OT\_FAULT, OCx overcurrent, gate low, V<sub>DD2</sub> UVLO, and ECC error) forces the driver off. During SPI communication, it is possible to mask faults shown on the fault pins. During SPI communication, any fault information on DRIVER\_FAULT or UVLO\_FAULT does not posted. When CS is brought low to initiate SPI communication, both DRIVER\_FAULT and UVLO\_FAULT are forced high.

**PROPAGATION DELAY RELATED PARAMETERS**

Propagation delay describes the time it takes a logic signal to propagate through a component. The propagation delay to a low output can differ from the propagation delay to a high output. The ADuM4137 specifies the rising propagation delay,  $t_{DLH}$  (see Figure 13), as the time between the rising input high logic threshold,  $V_{IH}$ , to the output rising 10% threshold. Likewise, the falling propagation delay,  $t_{DHL}$ , is defined as the time between the input falling logic low threshold,  $V_{IL}$ , and the output falling 90% threshold. The rise and fall times are dependent on the loading conditions and are not included in the propagation delay, which is the industry standard for gate drivers.

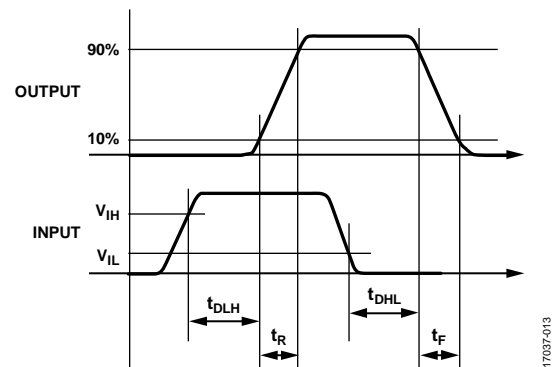


Figure 13. Propagation Delay Parameters

Propagation delay skew refers to the maximum amount that the propagation delay differs between multiple ADuM4137 components operating under the same temperature, input voltage, and load conditions.

## PROTECTION FEATURES

### Primary Side UVLO

The ADuM4137 has UVLO on both the primary and secondary sides. If the primary side voltage supply,  $V_{DD1}$ , drops below 4.25 V (typical), the transmission to the secondary side is stopped, effectively bringing the output low.

### Fault Reporting

The ADuM4137 provides protections for faults that may occur during the operation of an IGBT. The primary fault condition is overcurrent as detected by the overcurrent detection pins, OC1 and OC2. If detected, the ADuM4137 shuts the gate drive down and asserts the FAULT pin low. Faults initiate a soft shutdown through the  $V_{OFF\_SOFT}$  pin. During a fault, the external Miller clamp does not activate. Secondary undervoltage lock out (UVLO2), secondary thermal shutdown (TSD2), ECC error, overcurrent, gate low voltage detect, and remote overtemperature can initiate faults.

### Overcurrent Detection

The ADuM4137 operates with split emitter IGBTs or split source MOSFETs. Use the lower current section of the split leg switches for an accurate measurement of the current through the IGBT or MOSFET, resulting in a fast reaction to overcurrent events. When an overcurrent event is detected, a high speed, two-level turn off initiates. If the overcurrent condition remains beyond the two-level detect delay time ( $t_{dOC}$ ), a fault reports to the primary side of the ADuM4137. If the overcurrent condition is removed before the turn off time, the  $V_{OUT\_ON}$  pin returns to a high output state and the fault timer is reset.

The sense temperature on the TS1 pin can modify the overcurrent threshold. If the  $T\_RAMP\_OP$  bit is set to 1, the overcurrent threshold is set to 2 V (typical) across all operating conditions. When the  $T\_RAMP\_OP$  bit is set to 0, the overcurrent threshold,  $V_{OCD\_TH\_EN}$ , is 2.7 V typical at  $TS1 = 1.55$  V and 1.75 V typical at  $TS1 = 2.45$  V in a linear fashion (see Figure 14).

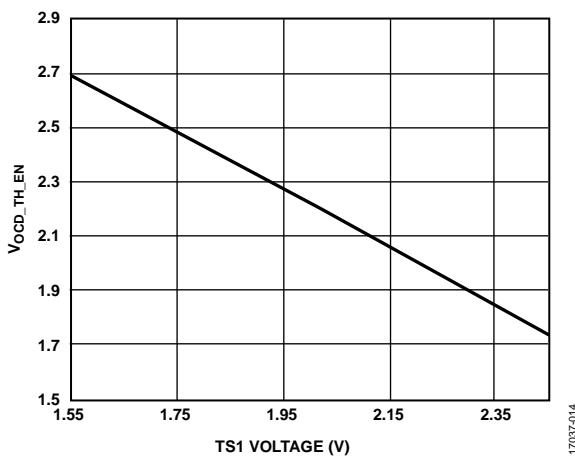


Figure 14. Overcurrent Threshold Variation Due to Sensed Temperature

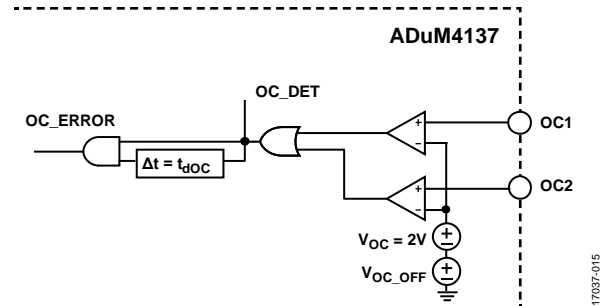


Figure 15. Split Emitter Overcurrent Detection Functional Block Diagram

### High Speed, Two-Level Turn Off

If the OC1 or OC2 pin detects an overcurrent, the two-level turn off circuitry drives the gate low. The internal NMOS FET drives the device gate low until the GATE\_SENSE pin reaches the 11.89 V (typical) voltage plateau.  $t_{dOCR}$  is the time the output takes from detecting an overcurrent to driving the overcurrent to the plateau voltage. After the detect time ( $t_{dOC}$ ), a fault is registered and reported to the primary side (see Figure 16). If during  $t_{dOC}$  the overcurrent threshold,  $V_{OCD\_TH}$ , is no longer violated, the internal PMOS returns the gate voltage back to the  $V_{DD2}$  voltage, and the two-level timer is reset (see Figure 17).

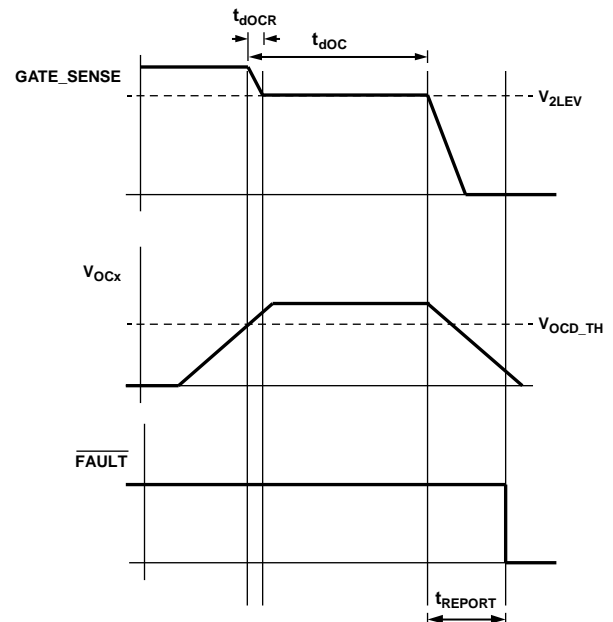


Figure 16. Two-Level Turn Off Fault Example (Not to Scale)

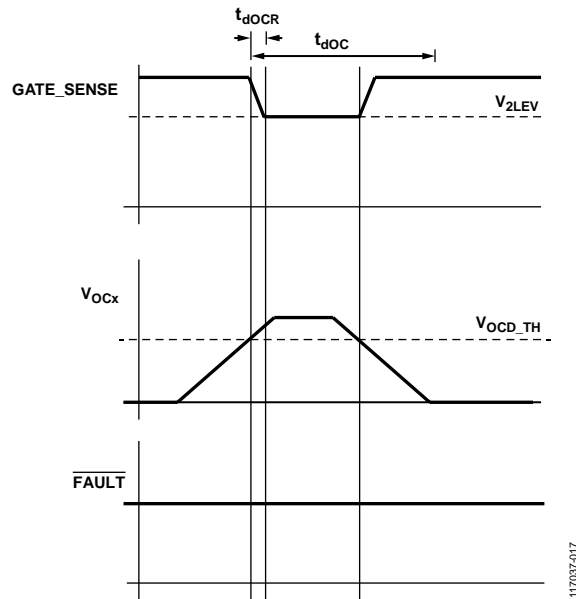


Figure 17. Two-Level Timer Recovery Example

117037-017

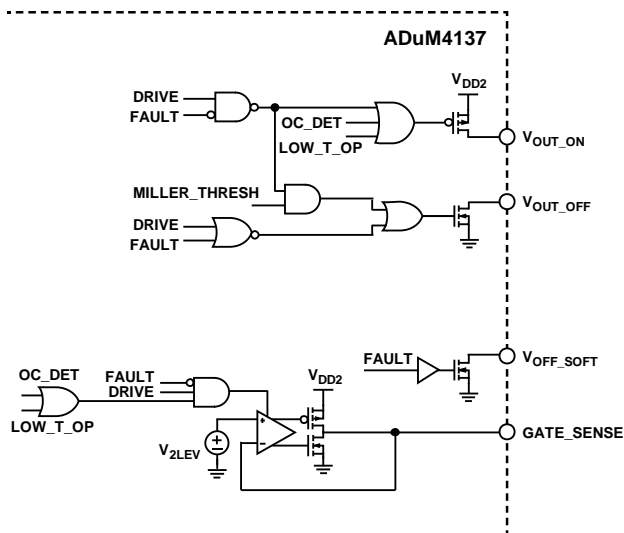


Figure 18. Gate Voltage Output Functional Block Diagram

117037-018

### Miller Clamp

The ADuM4137 has an integrated Miller clamp control signal to reduce voltage spikes on the IGBT gate due to the Miller capacitance during shutoff of the IGBT. When the input gate signal calls for the IGBT to turn off (drive low), the external Miller clamp MOSFET signal is initially off. When the voltage on the GATE\_SENSE pin crosses the 2 V (typical) internal voltage reference as referenced to GND<sub>2</sub>, the Miller clamp latches on for the remainder of the off time of the IGBT, creating a second low impedance current path for the gate current to follow. The Miller clamp switch remains on until the input drive signal changes from low to high. An example waveform of the timing is shown in Figure 19.

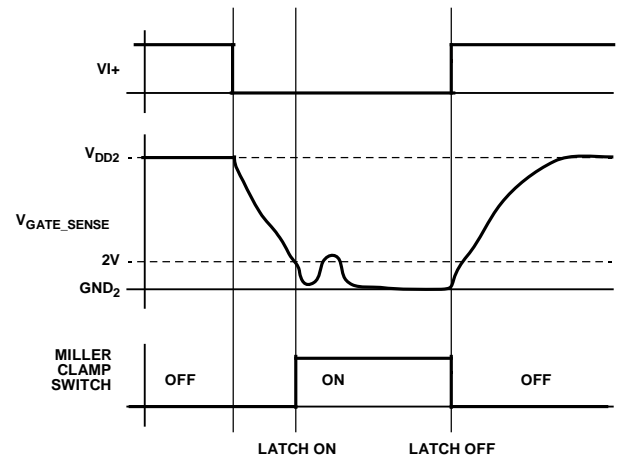


Figure 19. Miller Clamp Example

117037-019

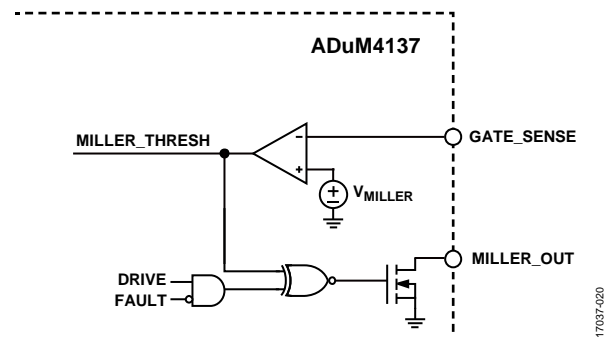


Figure 20. Miller Clamp Functional Block Diagram

117037-020

### Thermal Shutdown

The ADuM4137 contains two TSDs. If the internal temperature of the secondary side of the ADuM4137 exceeds 150°C (typical), the ADuM4137 enters a TSD fault, and the gate drive disables by means of a soft shutdown. When a TSD occurs, the ADuM4137 does not exit TSD until the internal temperature drops below 130°C (typical). After reaching this temperature, the ADuM4137 exits shutdown. A fault output is available on the primary side during a TSD event on the secondary side by means of the FAULT pin.

If the primary die temperature exceeds 154°C (typical), the primary side functions shut down, and shutting down the secondary side. The primary side leaves TSD when the internal temperature drops below 135°C (typical).

The main cause of overtemperature is driving too large a load for a given ambient temperature. This type of temperature overload typically affects the secondary side die because the main power dissipation for load driving occurs on the secondary side.

### ASC Pin Functionality

The ASC pin provides external secondary side control for enabling the driver. The ASC pin has a comparator triggering at 8.93 V (typical) with a 0.85 V (typical) hysteresis. When the ASC signal is greater than 8.93 V (typical), the signal forces the driver to output high if no fault occurs. The ASC pin signal is OR'ed with the forward path drive signal. Read and write capabilities via the SPI interface to the EEPROM on the secondary side are still available during an ASC event. Interfacing with the ASC pin can be performed directly or with an external open-drain NMOS MOSFET with a pull-up resistor to a value more than 8.93 V (typical). An internal pull-down current source is included on the ASC pin.

### Isolated Temperature Sensor

The ADuM4137 allows simple isolated temperature detection. Using an internal current source to bias an external temperature sensing diode, the ADuM4137 encodes the forward-biased voltage of the diode into a PWM signal that is passed across the isolation barrier from the secondary side to the primary side. The PWM signal operates at 10 kHz or 50 kHz (programmed in the EEPROM). Voltages between the minimum and maximum are approximately linear and monotonically interpolated. The ADuM4137 contains support for two remote temperature sensing diode assemblies, which can both cause overheating faults on the secondary side. Additionally, one temperature sensor readback is available for reading on the primary side through the isolated temperature reporting channel. The lower voltage (higher temperature) of the two temperature sensor pins, TS1 and TS2, report on the TEMP\_OUT pin. The gain and offset of the pulse-width modulated temperature sensor can be set in the EEPROM. A typical plot of the duty cycle vs. the lower temperature sense pin (TSx) voltage is shown in Figure 21.

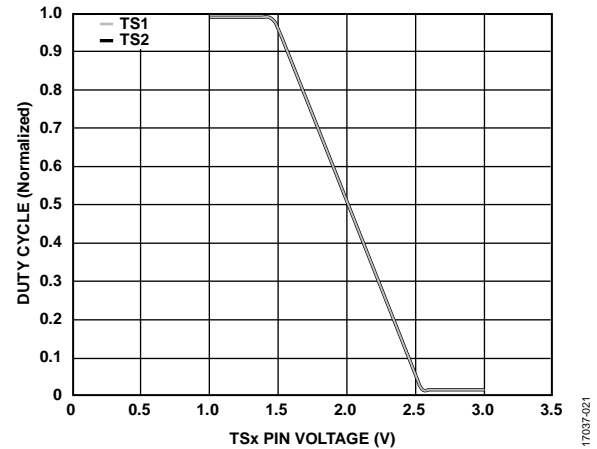


Figure 21. TEMP\_OUT Duty Cycle vs. Lower TSx Pin Voltage

The voltage mapping for the PWM follows this typical equation:

$$PWM\_DUTY = -0.9065 \times TS\_VOLTAGE + 2.3264$$

where:

*PWM\_DUTY* is the duty cycle on the TEMP\_OUT pin where full scale is 1. *PWM\_DUTY* is equivalent to the percent of duty cycle divided by 100.

*TS\_VOLTAGE* is the lowest voltage on the TS1 or the TS2 pin.

Use the GAIN\_1, GAIN\_2, OFFSET\_1, and OFFSET\_2 bits to adjust the voltage to the PWM response of the TSx pins. The gain and offset registers are 6-bit, twos complement values. The MSB is Bit 5 in each gain and offset bit field.

The gain bits affect the slope of the response, centered on 2.22 V (typical). This pivot point was selected to be approximately where a temperature sense diode stack may sit at 25°C. The gain bit values affect the slope of the response with a LSB of -0.00558 (typical). When the gain register changes, the response pivots such that the 2.22 V (typical) point returns a PWM of 0.194 (typical), unless an offset bit setting of a value other than 000000 is set. The offset bits shift the voltage to the PWM response up and down. The LSB of the offset bits is 0.001336 (typical).

Rewriting the PWM\_DUTY equation to allow gain and offset settings, and accounting for a 2.22 V typical pivot point in the gain setting results in the following:

$$PWM\_DUTY = (-0.9065 + GAIN\_x \times GAIN\_LSB) \times (TS\_VOLTAGE - 2.22) + (2.3264 + OFFSET\_x \times OFFSET\_LSB - 0.194)$$

where:

*GAIN\_x* is a GAIN\_1 or GAIN\_2 twos complement decimal equivalent.

*GAIN\_LSB* = -0.00558 typical.

*TS\_VOLTAGE* is the voltage seen on TS1 or TS2.

*OFFSET\_x* is the OFFSET\_1 or OFFSET\_2 twos complement decimal equivalent.

*OFFSET\_LSB* = 0.001336 typical.



### Low Temperature Operation Mode

A low temperature operation mode is available if the voltage sensed on the TS1 pin is greater than 2.4 V (typical), the maximum gate voltage is set to the two-level plateau voltage of 11.89 V (typical). Hysteresis allows continued low temperature operation until the TS1 pin voltage goes below 2.36 V (typical). Low temperature operation can be enabled or disabled in the EEPROM settings in the LOW\_T\_OP bit, Address 01, Bit 12. Basic operation is shown in Figure 22. During a two-level drive, the  $R_{DS(on)}$  resistances of the turn on and turn off drivers are increased to approximately 4 times the normal turn on and turn off resistances.

### FAULT Pin

The  $\overline{\text{FAULT}}$  pin can map to TSD, TSx\_OT\_FAULT, gate low,  $V_{DD2}$  UVLO, OCx overcurrent, and ECC error faults. The  $\overline{\text{FAULT}}$  pin is a CMOS output that is connected between the  $\text{GND}_1$  and  $V5_1$  pins. When  $\overline{\text{FAULT}}$  is brought low due to a fault detection on the ADuM4137, the output driver forward path is disabled, which brings the output low.

The latch time for the TSD, TSx\_OT\_FAULT,  $V_{DD2}$  UVLO, OCx overcurrent, and ECC error faults is 20 ms typical (Latch Assert Time B). The latch time for a gate low error is 26 ms typical (Latch Assert Time C). The  $\overline{\text{FAULT}}$  pin is held low for the hold time ( $t_{pw}$ ) or the length of time the error persists, whichever is longer.

### DRIVER\_FAULT Pin

The  $\overline{\text{DRIVER\_FAULT}}$  pin is an open-drain output with an internal pull-up current source ( $I_{PU\_DF}$ ) of 78  $\mu\text{A}$  (typical) to  $V5_1$ . The  $\overline{\text{DRIVER\_FAULT}}$  pin can map to the gate low, OCx overcurrent, ECC error, ASC, and DT\_FAULT faults. If any of the faults mapped to the  $\overline{\text{DRIVER\_FAULT}}$  occur, the  $\overline{\text{DRIVER\_FAULT}}$  pin is driven low for the minimum latch time or as long as the fault persists, whichever is longer. The minimum fault latch time for the gate low, OCx overcurrent, ECC error, and ASC is 26 ms (typical). The minimum fault latch time for a DT\_FAULT is 13 ms (typical) (Latch Assert Time A).

### UVLO\_FAULT Pin

The  $\overline{\text{UVLO\_FAULT}}$  pin can map to the gate low and  $V_{DD2}$  UVLO. The  $\overline{\text{UVLO\_FAULT}}$  pin is an open-drain output with an internal  $I_{PU\_DF}$  of 78  $\mu\text{A}$  (typical) to  $V5_1$ .

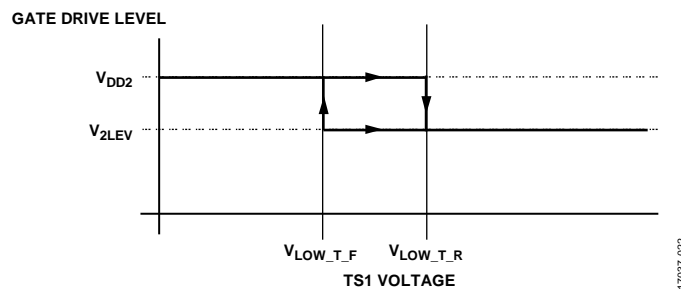


Figure 22. Low Temperature Operation

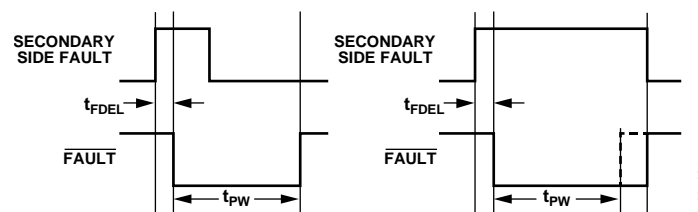
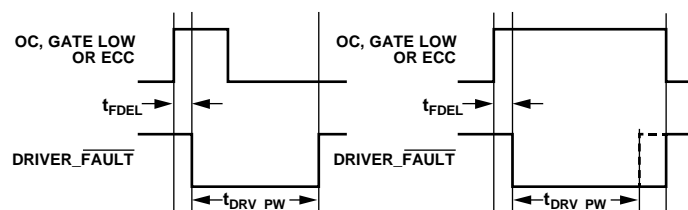


Figure 23.  $\overline{\text{FAULT}}$  Pin Fault



#### NOTES

1.  $t_{FDEL}$  IS THE REPORTING DELAY OF THE FAULT.
2. OC IS THE INTERNAL OVERCURRENT FAULT CONNECTION.
3.  $t_{DRV\_PW}$  IS THE DRIVE FAULT PULSE WIDTH LATCH TIME.

Figure 24.  $\overline{\text{DRIVER\_FAULT}}$  Fault

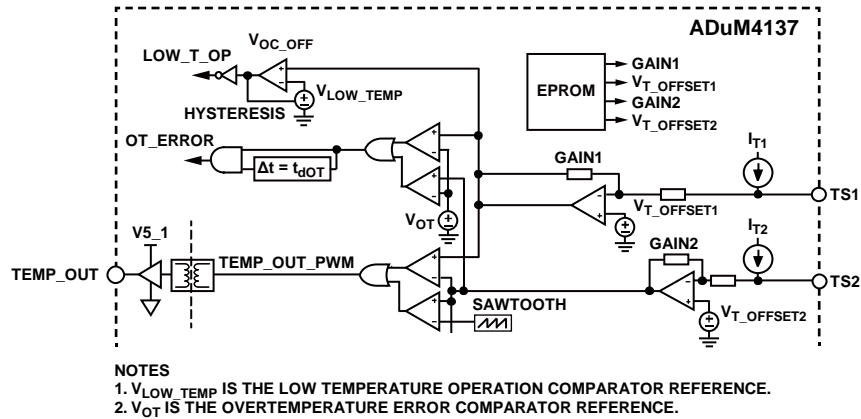
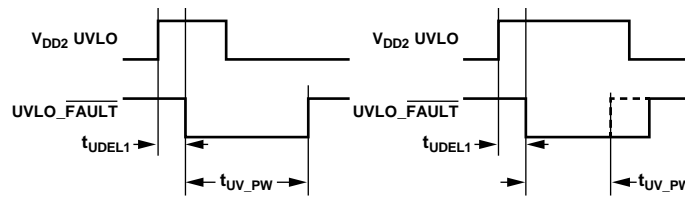
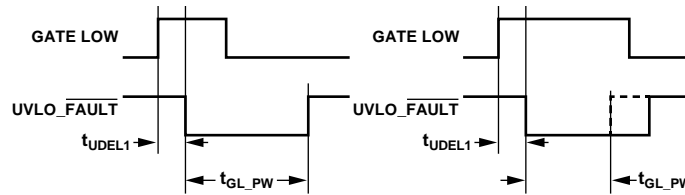


Figure 25. Remote Temperature Sensing Block Diagram



- NOTES**
1.  $t_{UV\_PW}$  IS THE  $V_{DD2}$  UVLO FAULT LATCH TIME, ~13ms TYPICAL.

Figure 26.  $\overline{UVLO\_FAULT}$  Fault for  $V_{DD2}$  UVLO

- NOTES**
1.  $t_{GL\_PW}$  IS THE GATE LOW FAULT LATCH TIME, ~26ms TYPICAL.

Figure 27.  $\overline{UVLO\_FAULT}$  Fault, Gate Low

### $V_{DD2}$ UVLO Fault

When a  $V_{DD2}$  UVLO fault occurs, the fault drives the  $\overline{UVLO\_FAULT}$  pin low within the fault propagation delay posting time,  $t_{UDEL1}$  (within 6.7  $\mu$ s typical) and reports the fault on the primary side for 13 ms (typical) if the  $V_{DD2}$  UVLO fault exists for less than ~13 ms. When the  $V_{DD2}$  UVLO fault exists for longer than ~13 ms, the  $\overline{UVLO\_FAULT}$  releases after the  $V_{DD2}$  UVLO is released on the secondary side.

### $\overline{UVLO\_FAULT}$ Fault, Gate Low

When a gate low fault occurs, the fault drives the  $\overline{UVLO\_FAULT}$  low within  $t_{UDEL1}$  and reports the fault on the primary side for ~26 ms if the  $V_{DD2}$  UVLO fault exists for less than ~26 ms. If the gate low fault exists for longer than ~26 ms, the  $\overline{UVLO\_FAULT}$  releases within  $t_{UDEL2}$  after the  $V_{DD2}$  UVLO releases on the secondary side. Separately, the pulse width can distinguish the gate low and  $V_{DD2}$  UVLO faults. However, if these faults occur simultaneously, only the longer pulse can be seen.



### Dead Time Control

Dead time ( $t_{DEXT}$ ) is set between  $VI+$  and  $VI-$ . If  $t_{DEXT} > \text{delay}$ , the dead time is set by  $t_{DEXT}$ . Otherwise, if less than or equal to the delay, the dead time is set by delay. Delay is 1  $\mu\text{s}$  typical.

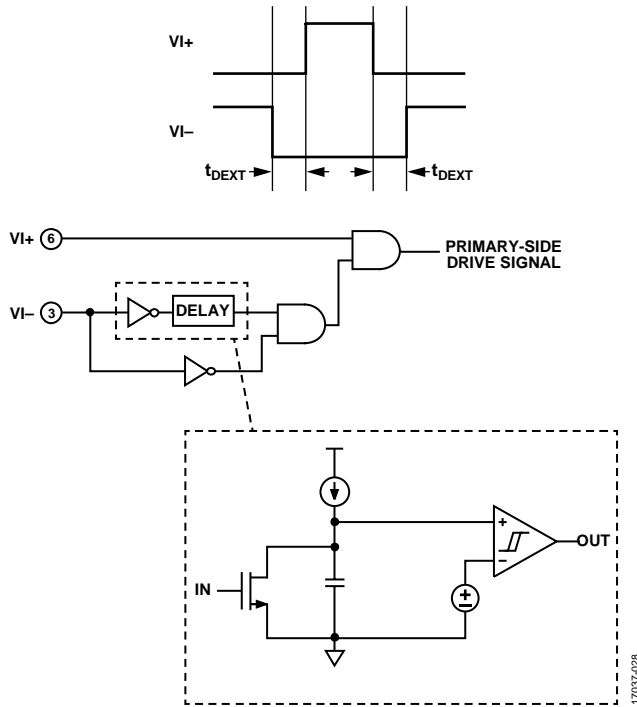


Figure 28. Dead Time Control

### DRIVER\_FAULT Fault, Dead Time Fault

The  $VI+$  signal is monitored as well as the internal dead time at the start of each cycle. If the  $VI+$  signal goes high before the rising edge of the 1  $\mu\text{s}$  internal dead time complete signal, a dead time fault issues. This fault latches on the primary side for approximately 13 ms and does not turn off the driver. If  $VI-$  is always kept low,  $VI+$  must be held low during startup.

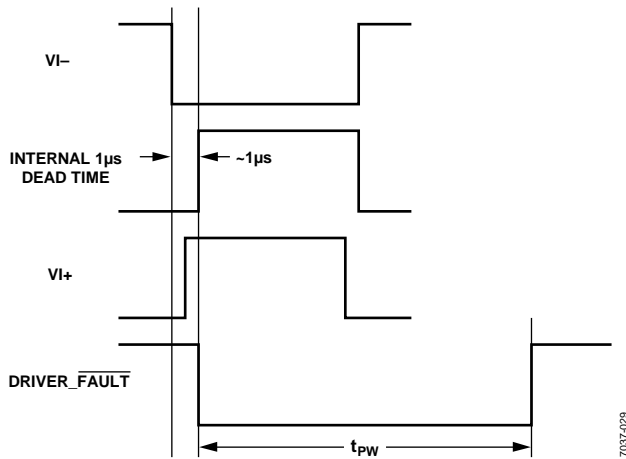


Figure 29. Dead Time Fault

### Power Dissipation

When driving an IGBT gate, the driver must dissipate power. This power can lead to TSD if the following considerations are not made. The gate of an IGBT can be simulated roughly as a capacitive load. Due to Miller capacitance and other nonlinearities, it is common practice to take the stated input capacitance ( $C_{ISS}$ ) of a given IGBT and multiply it by a factor of 5 to arrive at a conservative estimate to approximate the load being driven. With this value, the estimated total power dissipation ( $P_{DISS}$ ) in the system due to the switching action is given by the following equation:

$$P_{DISS} = C_{EST} \times (V_{DD2})^2 \times f_s$$

where:

$C_{EST} = C_{ISS} \times 5$  (conservative estimate).

$V_{DD2}$  is the voltage on the  $V_{DD2}$  pin.

$f_s$  is the switching frequency of the IGBT.

This power dissipation is shared between the internal on resistances of the internal gate driver switches and the external gate resistances ( $R_{GON}$  and  $R_{GOFF}$ ). The ratio of the internal gate resistances to the total series resistance allows the calculation of losses seen within the ADuM4137 chip.

Take the power dissipation found inside the chip due to switching, add the quiescent power losses, and multiply it by the  $\theta_{JA}$  value to product the rise above ambient temperature that the ADuM4137 experiences.

$$P_{DISS\_ADuM4137} = P_{DISS} \times 0.5(R_{DS(on)_P}/(R_{GON} + R_{DS(on)_P}) + (R_{DS(on)_N}/(R_{GOFF} + R_{DS(on)_N})) + P_{QUIESCENT}$$

where:

$P_{DISS\_ADuM4137}$  is the power dissipation of the ADuM4137.

$R_{GON}$  is the external series resistance in the on path.

$R_{GOFF}$  is the external series resistance in the off path.

$P_{QUIESCENT}$  is the quiescent power.

$$T_{ADuM4137} = \theta_{JA} \times P_{DISS\_ADuM4137} + T_{AMB}$$

where:

$T_{ADuM4137}$  is the junction temperature of the ADuM4137.

$T_{AMB}$  is the ambient temperature.

For the ADuM4137 to remain within specification,  $T_{ADuM4137}$  must not exceed 150°C (typical). If  $T_{ADuM4137}$  exceeds 150°C (typical), the ADuM4137 enters TSD.

## INSULATION LIFETIME

All insulation structures eventually break down when subjected to voltage stress over a sufficiently long period. The rate of insulation degradation is dependent on the characteristics of the voltage waveform applied across the insulation. In addition to the testing performed by the regulatory agencies, Analog Devices carries out an extensive set of evaluations to determine the lifetime of the insulation structure within the ADuM4137.

Analog Devices performs accelerated life testing using voltage levels higher than the rated continuous working voltage. Acceleration factors for several operating conditions are determined. These factors allow calculation of the time to failure at the actual working voltage.

The values shown in Table 10 summarize the peak voltage for 20 years of service life for a bipolar ac operating condition, and the maximum CSA and VDE approved working voltages. In many cases, the approved working voltage is higher than the 20 year service life voltage. Operation at these high working voltages can lead to shortened insulation life in some cases.

The insulation lifetime of the ADuM4137 depends on the voltage waveform type imposed across the isolation barrier. The iCoupler insulation structure degrades at different rates depending on whether the waveform is bipolar ac, unipolar ac, or dc. Figure 30, Figure 31, and Figure 32 show these different isolation voltage waveforms.

A bipolar ac voltage environment is the worst case for the iCoupler products and is the 20 year operating lifetime that Analog Devices recommends for maximum working voltage. In the case of unipolar ac or dc voltage, the stress on the insulation is significantly lower, which allows operation at higher working voltages while still achieving a 20 year service life. Treat any cross insulation voltage waveform that does not conform to Figure 31 or Figure 32 as a bipolar ac waveform, and limit its peak voltage to the 20 year lifetime voltage value listed in Table 10.

The voltage presented in Figure 31 is shown as sinusoidal only for illustration purposes. It is meant to represent any voltage waveform varying between 0 V and some limiting value. The limiting value can be positive or negative, but the voltage cannot cross 0 V.

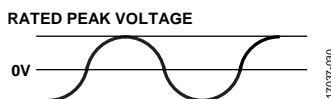


Figure 30. Bipolar AC Waveform

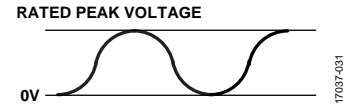


Figure 31. Unipolar AC Waveform

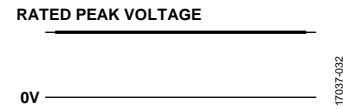


Figure 32. DC Waveform

## DC CORRECTNESS AND MAGNETIC FIELD IMMUNITY

The ADuM4137 is resistant to external magnetic fields. The limitation on the ADuM4137 magnetic field immunity is set by the condition in which the induced voltage in the transformer receiving coil is sufficiently large to either falsely set or reset the decoder. The following analysis defines the conditions under which this can occur.

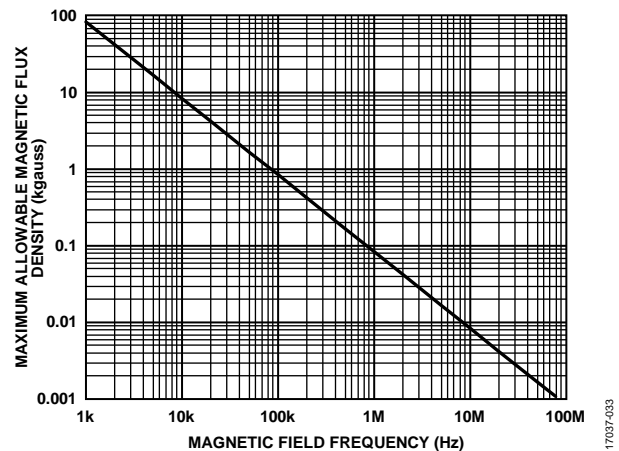


Figure 33. Maximum Allowable External Magnetic Flux Density

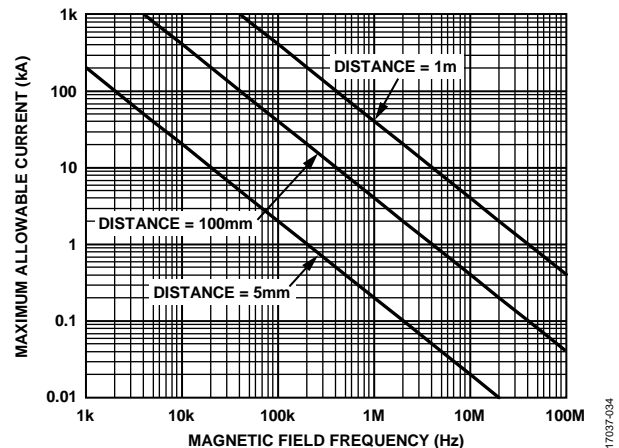
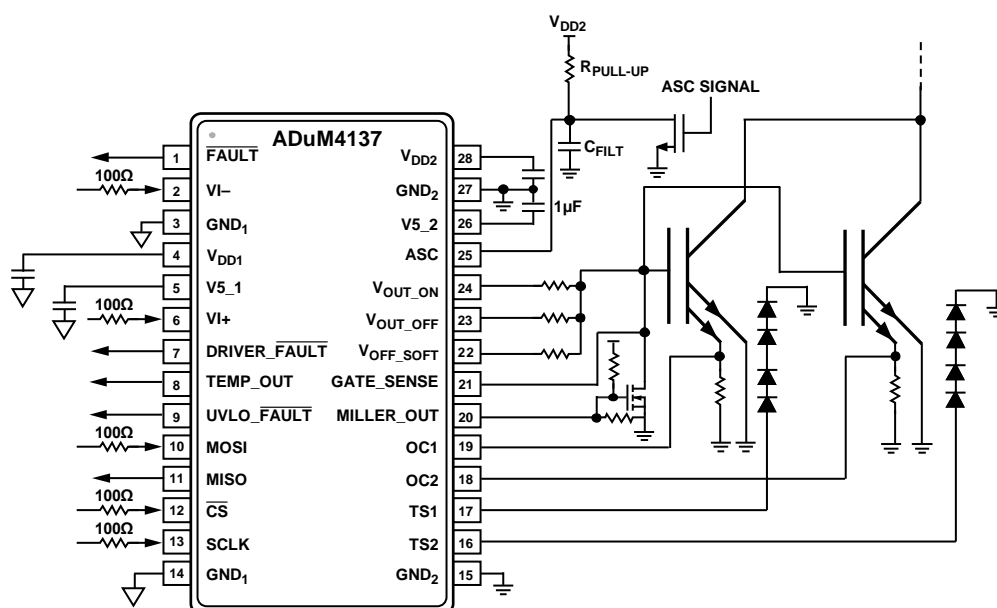


Figure 34. Maximum Allowable Current for Various Current to ADuM4137 Spacings

## TYPICAL APPLICATION CIRCUIT



## NOTES

1. C<sub>FILT</sub> IS THE ASC PIN FILTER CAPACITOR.
2. R<sub>PULL-UP</sub> IS THE ASC PIN PULL-UP RESISTOR

Figure 35. IGBT Drive Example Application

17037-035

## OUTLINE DIMENSIONS

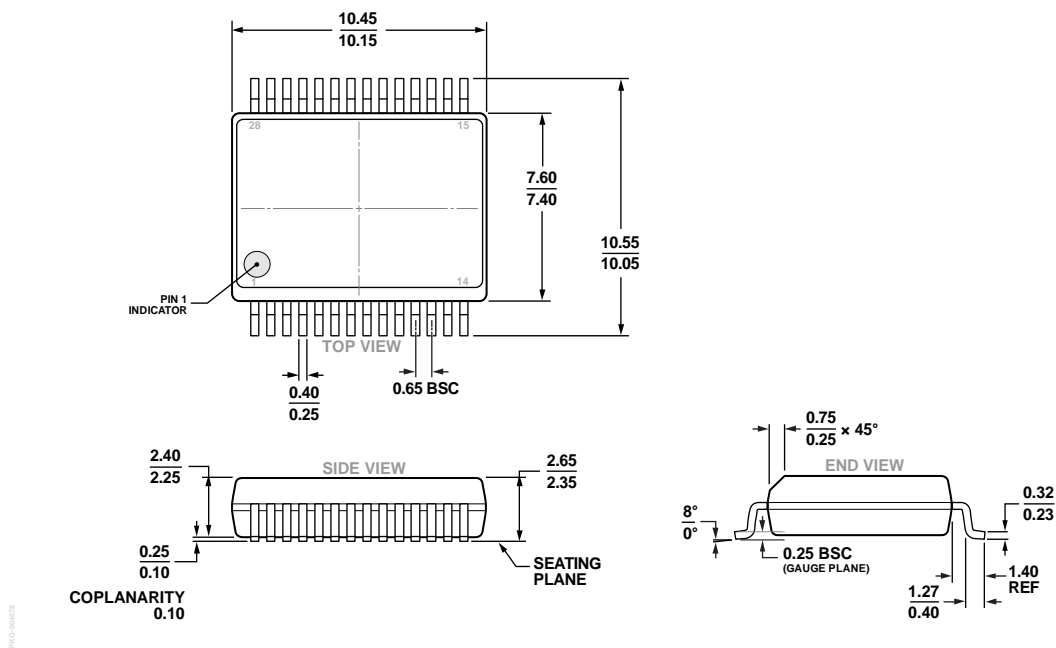


Figure 36. 28-Lead Standard Small Outline, Wide Body, with Finer Pitch [SOIC\_W\_FP]  
(RN-28-1)

Dimensions shown in millimeters

## ORDERING GUIDE

Model <sup>1, 2</sup>	Temperature Range	Package Description	Package Option
ADuM4137WBRNZ	−40°C to +125°C	28-Lead Standard Small Outline, Wide Body, with Finer Pitch [SOIC_W_FP]	RN-28-1
ADuM4137WBRNZ-RL	−40°C to +125°C	28-Lead Standard Small Outline, Wide Body, with Finer Pitch [SOIC_W_FP], 13" Tape and Reel	RN-28-1
EVAL-ADuM4137EBZ		Evaluation Board	

<sup>1</sup> Z = RoHS Compliant Part.

<sup>2</sup> W = Qualified for Automotive Applications.

## AUTOMOTIVE PRODUCTS

The ADuM4137W models are available with controlled manufacturing to support the quality and reliability requirements of automotive applications. Note that these automotive models may have specifications that differ from the commercial models; therefore, designers should review the Specifications section of this data sheet carefully. Only the automotive grade products shown are available for use in automotive applications. Contact your local Analog Devices account representative for specific product ordering information and to obtain the specific Automotive Reliability reports for these models.



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